OPAx994 32V、レール ツー レール入出力、24MHz、125mA 出力電流オペアンプ、無制限の容量性負荷駆動付き

1 特長

- 広い電源電圧範囲:2.7V～32V
- レール ツー レール入出力
- 広い帯域幅:24MHz GBW、ユニティ ゲインで安定
- 無制限の容量性負荷駆動能力:
  - 10µF、1MΩ の負荷を駆動した場合の位相マージンは 50°
- 大出力電流の駆動:±125mA
- 低いオフセット電圧:±350µV (標準値)
- 低いオフセット電圧ドリフト:±2.5µV/°C (標準値)
- 低ノイズ:1kHz で 12nV/√Hz
- 大きい同相除去:125dB
- 高いスルーレート:35V/µs
- 低い静止電流:アンプ 1 個あたり 1.35mA

2 アプリケーション

- AC 充電 (パイル) ステーション
- GFCI 故障検出およびテスト
- ソフトウェア無線
- PC とノート PC 向けのディスプレイ・パネル
- LCD TV
- 無線制御照明
- モーター・ドライブ:出力段と制御モジュール
- パワー・デリバリ:UPS 、サーバー、商用ネットワークの電源
- ADC ドライバとリファレンス・バッファ・アンプ
- ハイサイドおよびローサイド電流検出

3 概要

OPAx994 ファミリ (OPA994 および OPA2994) は、高電圧 (32V) レール・ツー・レール入出力 (RRIO) オペアンプのファミリです。これらのデバイスは、24MHz の広いユニティ ゲイン帯域幅と 35V/µs の高いスルーレートを含む優れた AC 性能を実現しながら、チャネルあたり 1.35mA の静止電流しか必要としません。

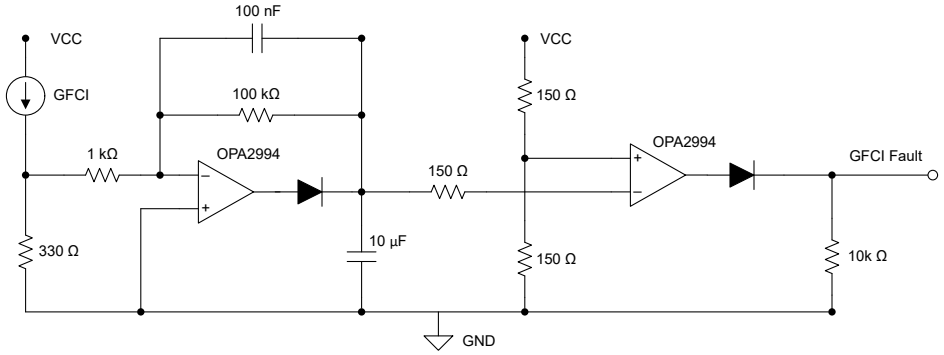
OPAx994 ファミリは、幅広い容量性負荷にわたって安定性を維持するように設計されています。たとえば、OPAx994 は、1MΩ の負荷抵抗で 10µF の大きな容量性負荷を駆動する場合、50 度の位相マージンを達成できます。OPAx994 は、大きな容量性負荷に対する持続的なリンギングを緩和する補償アーキテクチャを使用して設計されています。これにより、大規模な、変動する、または未知の容量性負荷を持つシステムに対して、信頼性の高い性能と容易な設計が可能になります。

また、これらのデバイスは、125mA/チャネルの高い短絡出力電流、低いオフセット電圧 (±350µV、標準値)、低いオフセットのドリフト (±2.5µV/°C、標準値)、メイン入力ペア内の高電圧動作に対する 125dB の高い CMRR など、優れた DC 精度を提供します。これにより、OPAx994 は高電圧産業用アプリケーション向けの柔軟で堅牢な高性能オペアンプになります。

パッケージ情報

部品番号 (1)	チャネル数	パッケージ	パッケージ サイズ (2)
OPA994	シングル	DBV (SOT-23、5)	2.9mm × 2.8mm
		DCK (SC70、5)	2mm × 2.1mm
		D (SOIC、8)	4.9mm × 6mm
OPA2994	デュアル	D (SOIC、8)	4.9mm × 6mm
		DGK (VSSOP、8)	3mm × 4.9mm
		DDF (SOT-23、8)	2.9mm × 2.8mm

(1) 詳細については、セクション 10 を参照してください。
(2) パッケージ サイズ (長さ × 幅) は公称値であり、該当する場合はピンも含まれます。



電気自動車サービス機器 (EVSE) の漏電遮断器 (GFCI) 故障検出およびテスト回路の OPAx994

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4 Pin Configuration and Functions

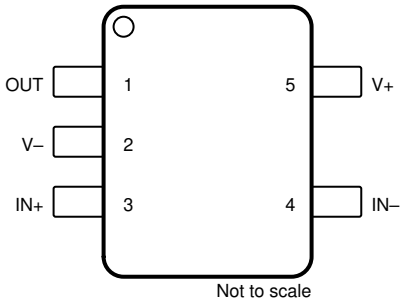


図 4-1. OPA994 DBV Package
5-Pin SOT-23
(Top View)

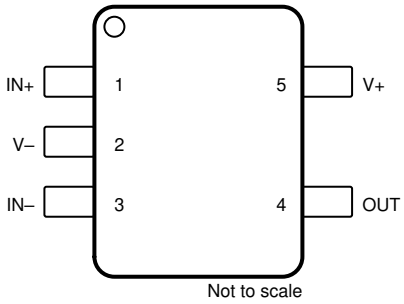
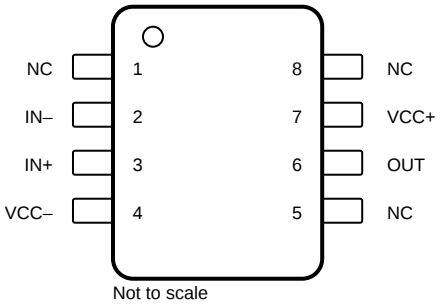


図 4-2. OPA994 DCK Package
5-Pin SC70
(Top View)



NC- no internal connection

図 4-3. OPA994 D Package
8-Pin SOIC
(Top View)

表 4-1. Pin Functions: OPA994

PIN				TYPE(1)	DESCRIPTION
NAME	DBV	DCK	D		
IN–	4	3	2	I	Inverting input
IN+	3	1	3	I	Noninverting input
NC	—	—	8	—	Do not connect
NC	—	—	1	—	Do not connect
NC	—	—	5	—	Do not connect
OUT	1	4	6	O	Output
V–	2	2	4	—	Negative (lowest) power supply
V+	5	5	7	—	Positive (highest) power supply

(1) I = input, O = output

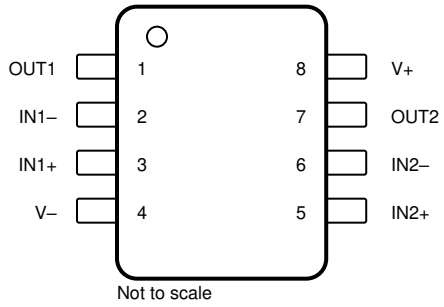


図 4-4. OPA2994 D, DGK and DDF Package, 8-Pin SOIC, VSSOP and SOT-23 (Top View)

表 4-2. Pin Functions: OPA2994

PIN		TYPE(1)	DESCRIPTION
NAME	NO.		
IN1+	3	I	Noninverting input, channel 1
IN1–	2	I	Inverting input, channel 1
IN2+	5	I	Noninverting input, channel 2
IN2–	6	I	Inverting input, channel 2
OUT1	1	O	Output, channel 1
OUT2	7	O	Output, channel 2
V+	8	—	Positive (highest) power supply
V–	4	—	Negative (lowest) power supply

(1) I = input, O = output

5 Specifications

5.1 Absolute Maximum Ratings

over operating ambient temperature range (unless otherwise noted)(1)

		MIN	MAX	UNIT
Supply voltage, V_S = (V+) – (V–)		0	33	V
Signal input pins	Common-mode voltage(3)	(V–) – 0.5	(V+) + 0.5	V
	Differential voltage(4)		±10	V
	Current(3)		±10	mA
Output short-circuit(2)		Continuous		
Junction temperature, T_J			150	°C
Storage temperature, T_{stg}		–65	150	°C

(1) Operating the device beyond the ratings listed under *Absolute Maximum Ratings* will cause permanent damage to the device. These are stress ratings only, based on process and design limitations, and this device has not been designed to function outside the conditions indicated under *Recommended Operating Conditions*. Exposure to any condition outside *Recommended Operating Conditions* for extended periods, including absolute-maximum-rated conditions, may affect device reliability and performance.
(2) Short-circuit to ground, one amplifier per package. Extended short-circuit current, especially with higher supply voltage, can cause excessive heating and eventual destruction.
(3) Input pins are diode-clamped to the power-supply rails. Input signals that may swing more than 0.5V beyond the supply rails must be current limited to 10mA or less.
(4) Input pins are connected by back-to-back diodes for input protection. If the differential input voltage may exceed 0.5V, limit the input current to 10mA or less.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001(1)	±4000	V
		Charged-device model (CDM), per ANSI/ESDA/JEDEC JS-002(2)	±1500	

(1) JEDEC document JEP155 states that 500V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250V CDM allows safe manufacturing with a standard ESD control process.

5.3 Recommended Operating Conditions

over operating ambient temperature range (unless otherwise noted)

		MIN	MAX	UNIT
V_S	Supply voltage, (V+) – (V–)	2.7	32	V
V_I	Common mode voltage range	(V–) – 0.1	(V+) + 0.1	V
T_A	Specified temperature	–40	125	°C

5.4 Thermal Information for Single Channel

THERMAL METRIC[1]		OPA994			UNIT
		D (SOIC)	DCK (SC70)	DBV (SOT-23)	
		8 PINS	5 PINS	5 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	133.5	214.2	185.4	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	75.8	129.2	82.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	76.9	67.5	51.6	°C/W
ψ_{JT}	Junction-to-top characterization parameter	26.4	42.7	19.5	°C/W
ψ_{JB}	Junction-to-board characterization parameter	76.2	67.1	51.2	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application note.

5.5 Thermal Information for Dual Channel

THERMAL METRIC[1]		OPA2994			Unit
		D (SOIC)	DGK (VSSOP)	DDF (SOT-23)	
		8 PINS	8 PINS	8 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	124.0	169.6	125.2	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	67.3	61.6	63.8	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	68.4	91.2	45.2	°C/W
ψ_{JT}	Junction-to-top characterization parameter	19.9	9.0	2.8	°C/W
ψ_{JB}	Junction-to-board characterization parameter	67.6	89.7	45.0	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the *Semiconductor and IC Package Thermal Metrics* application note.

5.6 Electrical Characteristics

For V_S = (V+) – (V–) = 2.7V to 32V (±1.35V to ±16V) at T_A = 25°C, R_L = 10kΩ connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
OFFSET VOLTAGE							
V_{OS}	Input offset voltage	V_{CM} = V–			±0.35	±2.3	mV
			T_A = –40°C to 125°C			±3.3	
dV_{OS}/dT	Input offset voltage drift	V_{CM} = V–	T_A = –40°C to 125°C		±2.5		µV/°C
PSRR	Input offset voltage versus power supply	V_{CM} = V–, V_S = 5V to 32V	T_A = –40°C to 125°C		±3.5	±22	µV/V
		V_{CM} = V–, V_S = 2.7V to 32V	T_A = –40°C to 125°C			±60(1)	µV/V
	DC channel separation				1		µV/V
INPUT BIAS CURRENT							
I_B	Input bias current				±400	±1500	nA
I_{OS}	Input offset current				±7		nA
NOISE							
E_N	Input voltage noise	f = 0.1Hz to 10Hz			1.8		$µV_{PP}$
					0.3		$µV_{RMS}$
e_N	Input voltage noise density	f = 1kHz			12		nV/√Hz
		f = 10kHz			11		
i_N	Input current noise density	f = 1kHz			1		pA/√Hz
INPUT VOLTAGE RANGE							
V_{CM}	Common-mode input voltage range			(V–) – 0.1		(V+) + 0.1	V
CMRR	Common-mode rejection ratio	V_S = 32V, V– < V_{CM} < (V+) – 2V (Main Input Pair)	T_A = –40°C to 125°C	109	125		dB
		V_S = 5V, V– < V_{CM} < (V+) – 2V (Main Input Pair)(1)	T_A = –40°C to 125°C	93	111		
		V_S = 2.7V, V– < V_{CM} < (V+) – 2V (Main Input Pair)	T_A = –40°C to 125°C		114		
		V_S = 2.7 – 32V, (V+) – 1V < V_{CM} < V+ (Aux Input Pair)	T_A = –40°C to 125°C		77		
		(V+) – 2V < V_{CM} < (V+) – 1V	T_A = –40°C to 125°C	See Offset Voltage vs Common-Mode Voltage (Transition Region)			
INPUT IMPEDANCE							
Z_{ID}	Differential				0.2 || 1		MΩ || pF
Z_{ICM}	Common-mode				2 || 0.5		GΩ || pF
OPEN-LOOP GAIN							
A_{OL}	Open-loop voltage gain	V_S = 32V, V_{CM} = V_S / 2, (V–) + 1V < V_O < (V+) – 1V		80	87		dB
			T_A = –40°C to 125°C		87		
		V_S = 5V, V_{CM} = V_S / 2, (V–) + 1V < V_O < (V+) – 1V(1)		75	80		
			T_A = –40°C to 125°C		80		
		V_S = 2.7V, V_{CM} = V_S / 2, (V–) + 1V < V_O < (V+) – 1V(1)		75	80		
			T_A = –40°C to 125°C		80		

5.6 Electrical Characteristics (続き)

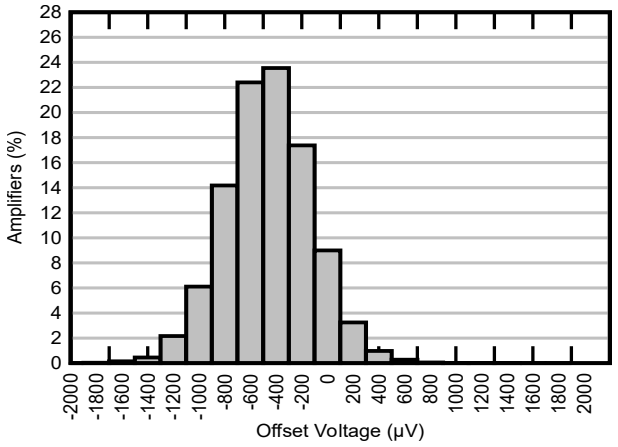
For V_S = (V+) – (V–) = 2.7V to 32V (±1.35V to ±16V) at T_A = 25°C, R_L = 10kΩ connected to V_S / 2, V_{CM} = V_S / 2, and V_{OUT} = V_S / 2, unless otherwise noted.

PARAMETER		TEST CONDITIONS		MIN	TYP	MAX	UNIT
FREQUENCY RESPONSE							
GBW	Gain-bandwidth product				24		MHz
SR	Slew rate	V_S = 32V, V_{STEP} = 10V, G = +1, C_L = 20pF			35		V/µs
t_S	Settling time	To 0.1%, V_S = 32V, V_{STEP} = 10V, G = +1, C_L = 50pF			0.43		µs
		To 0.1%, V_S = 32V, V_{STEP} = 10V, G = +1, C_L = 500pF			0.45		
		To 0.01%, V_S = 32V, V_{STEP} = 10V, G = +1, C_L = 50pF			0.77		
		To 0.01%, V_S = 32V, V_{STEP} = 10V, G = +1, C_L = 500pF			0.85		
	Phase margin	G = +1, R_L = 10kΩ, C_L = 20pF			50		°
	Overload recovery time	V_{IN} × gain > V_S			130		ns
THD+N	Total harmonic distortion + noise	V_S = 32V, V_O = 3V_{RMS}, G = 1, f = 1kHz, R_L = 10kΩ			0.00022		%
					113		dB
OUTPUT							
	Voltage output swing from rail	Positive and negative rail headroom	V_S = 32V, R_L = no load		20		mV
			V_S = 32V, R_L = 10kΩ		58	68	
			V_S = 32V, R_L = 2kΩ		117	137	
			V_S = 5V, R_L = no load		30		
			V_S = 5V, R_L = 10kΩ		45	52	
			V_S = 5V, R_L = 2kΩ		25	60	
			V_S = 2.7V, R_L = no load		25		
			V_S = 2.7V, R_L = 10kΩ		42	48	
			V_S = 2.7V, R_L = 2kΩ		45	54	
I_{SC}	Short-circuit current	V_S = 32V		±62	±125		mA
		V_S = 5V(1)		±50	±85		
		V_S = 2.7V(1)		±30	±60		
C_{LOAD}	Capacitive load drive			Unlimited; See Phase Margin vs Capacitive Load			pF
Z_O	Open-loop output impedance	I_O = 0A		See Open-Loop Output Impedance vs Frequency			Ω
POWER SUPPLY							
I_Q	Quiescent current per amplifier	V_{CM} = V-, I_O = 0A			1.35	1.93	mA
			T_A = –40°C to 125°C			2.23	mA

(1) Specified by characterization only.

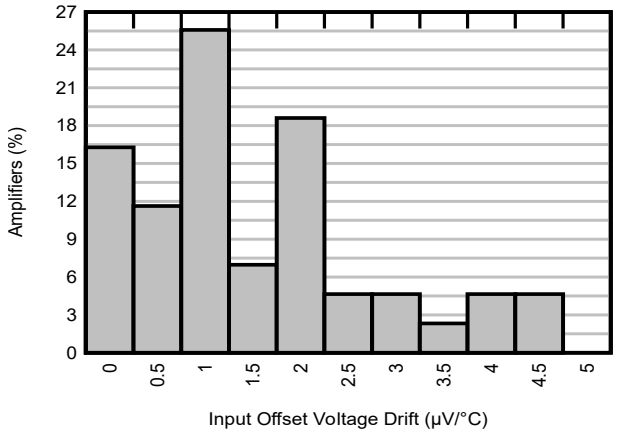
5.7 Typical Characteristics

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)



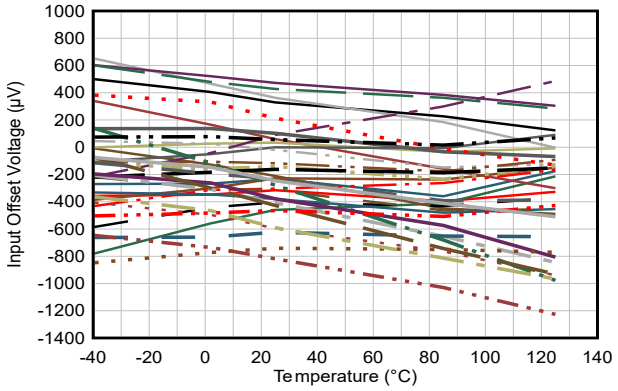
Distribution from 17,184 amplifiers

図 5-1. Offset Voltage Production Distribution



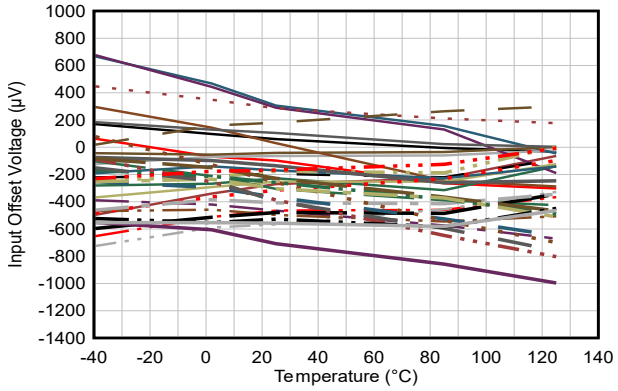
Distribution from 43 amplifiers
T_A = -40°C to 125°C

図 5-2. Offset Voltage Drift Distribution



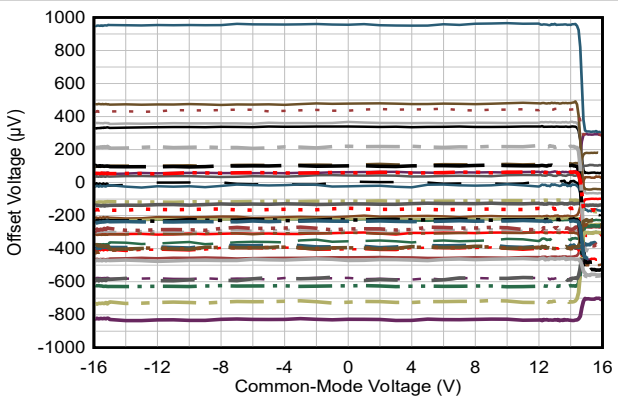
V_{CM} = V-
Each line represents one channel

図 5-3. Offset Voltage vs Temperature



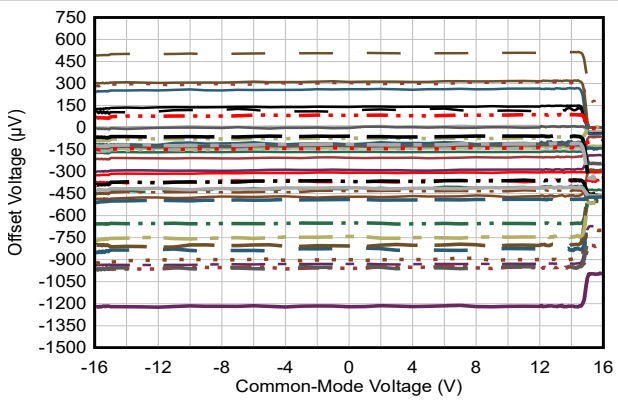
V_{CM} = V+
Each line represents one channel

図 5-4. Offset Voltage vs Temperature



Each line represents one channel
T_A = 25°C

図 5-5. Offset Voltage vs Common-Mode Voltage



Each line represents one channel
T_A = 125°C

図 5-6. Offset Voltage vs Common-Mode Voltage

5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)

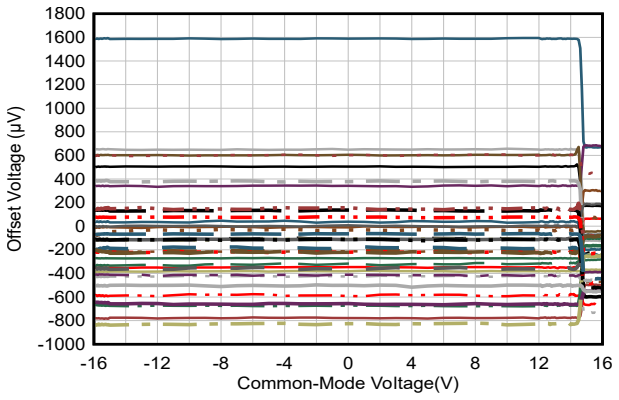


図 5-7. Offset Voltage vs Common-Mode Voltage

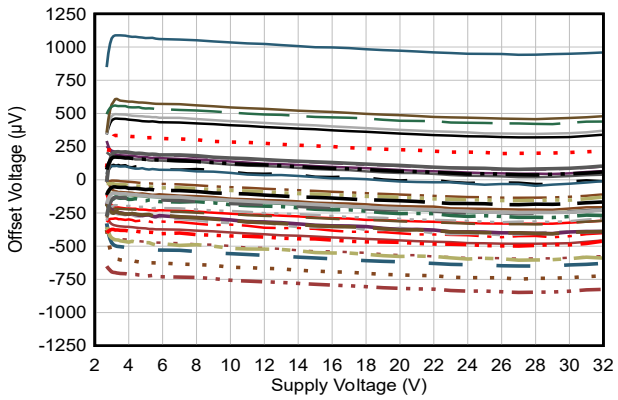


図 5-8. Offset Voltage vs Power Supply

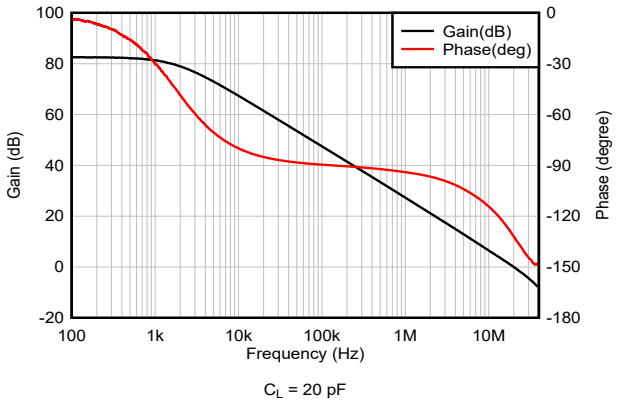


図 5-9. Open-Loop Gain and Phase vs Frequency

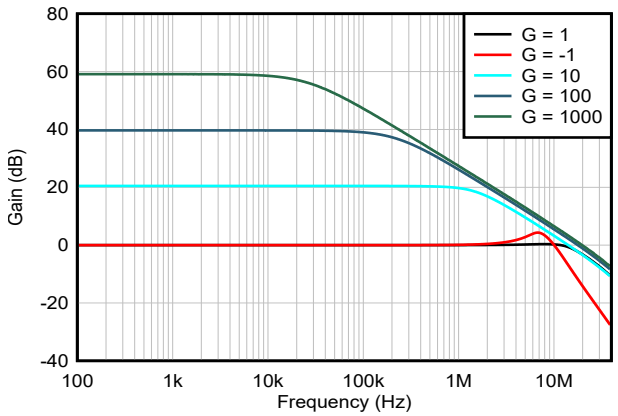


図 5-10. Closed-Loop Gain vs Frequency

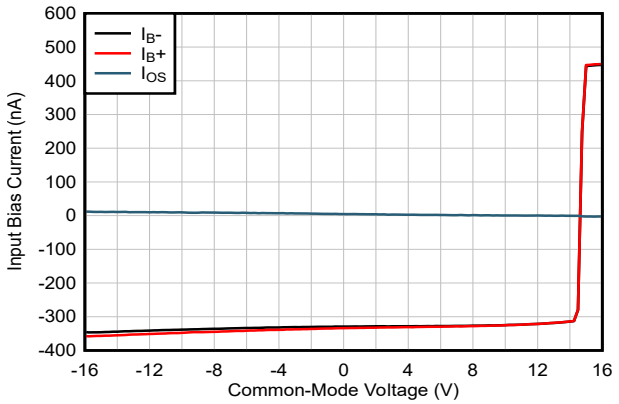


図 5-11. Input Bias Current and Offset Current vs Common-Mode Voltage

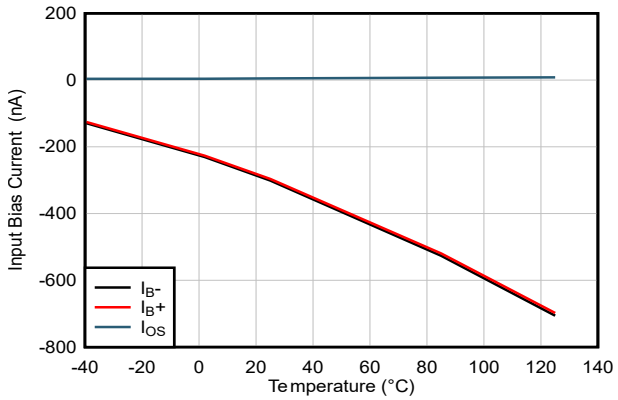
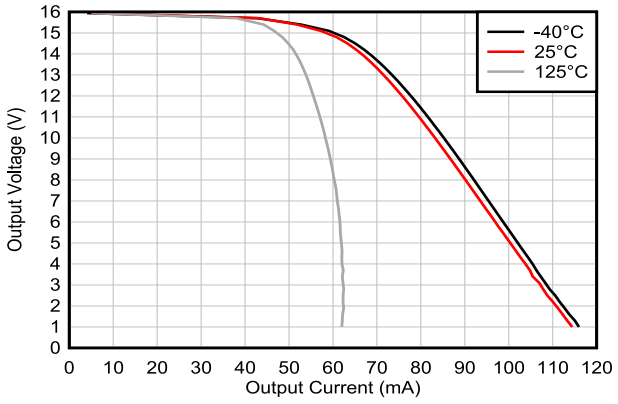


図 5-12. Input Bias Current and Offset Current vs Temperature

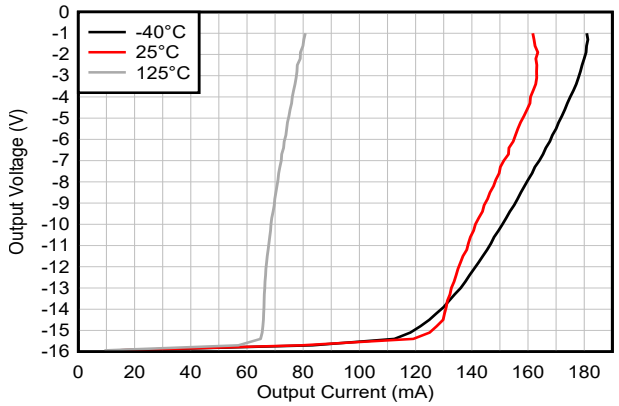
5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)



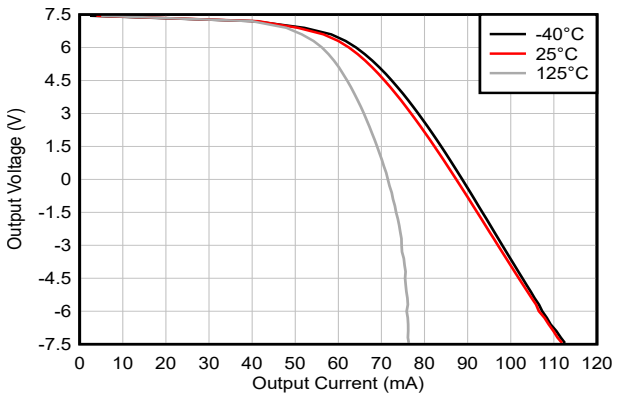
V_S = 32 V

図 5-13. Output Voltage Swing vs Output Current (Sourcing)



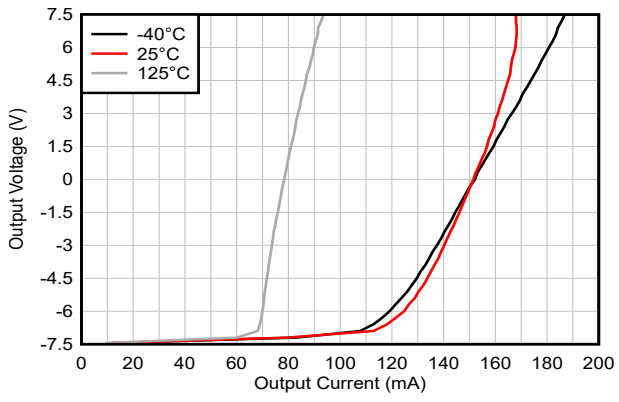
V_S = 32 V

図 5-14. Output Voltage Swing vs Output Current (Sinking)



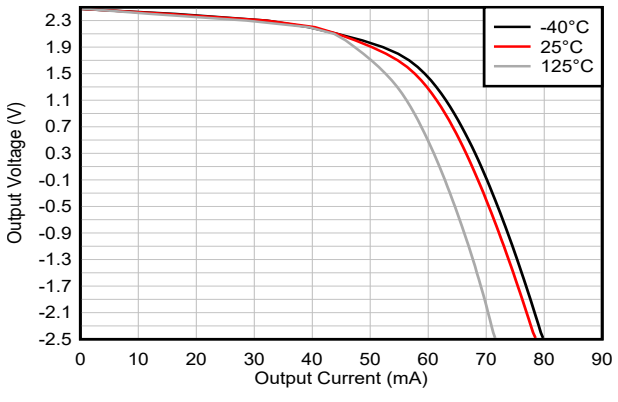
V_S = 15 V

図 5-15. Output Voltage Swing vs Output Current (Sourcing)



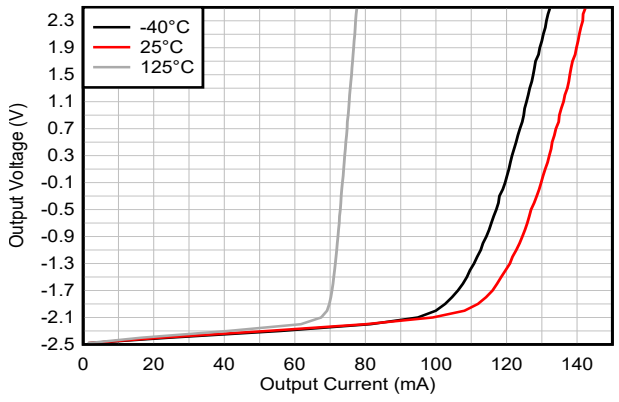
V_S = 15 V

図 5-16. Output Voltage Swing vs Output Current (Sinking)



V_S = 5 V

図 5-17. Output Voltage Swing vs Output Current (Sourcing)

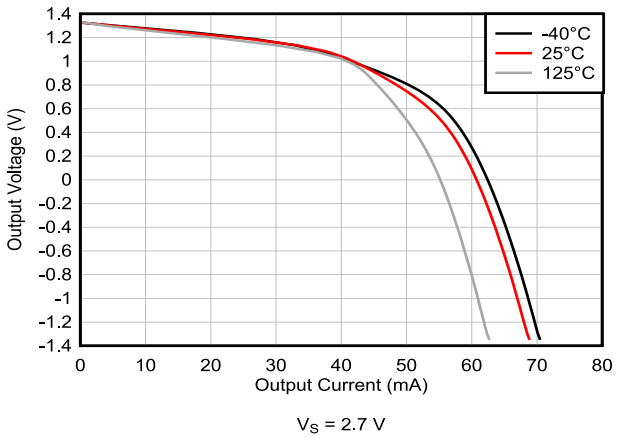


V_S = 5 V

図 5-18. Output Voltage Swing vs Output Current (Sinking)

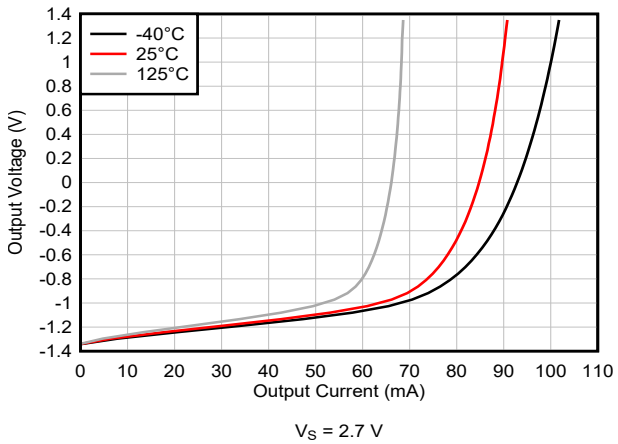
5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)



V_S = 2.7 V

図 5-19. Output Voltage Swing vs Output Current (Sourcing)



V_S = 2.7 V

図 5-20. Output Voltage Swing vs Output Current (Sinking)

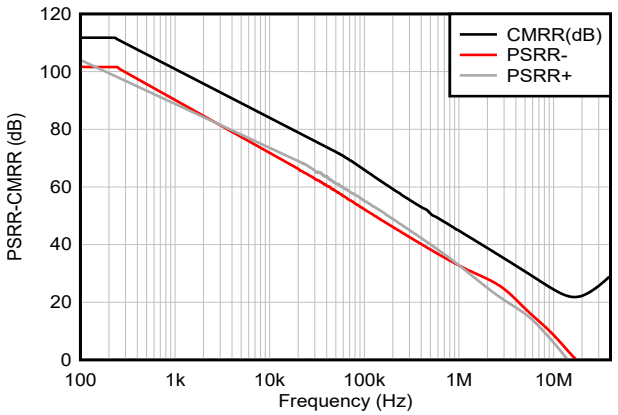
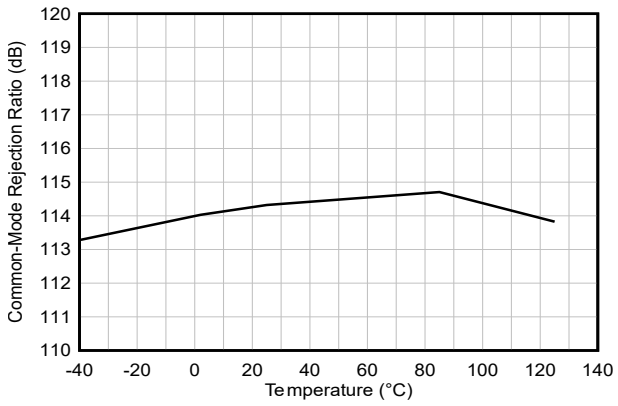
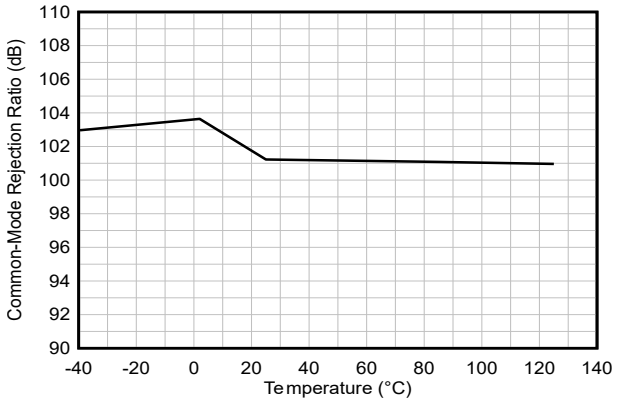


図 5-21. CMRR and PSRR vs Frequency



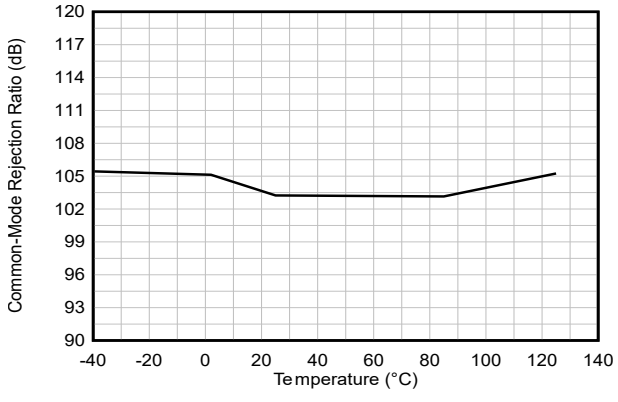
f = 0 Hz

図 5-22. CMRR vs Temperature



V_S = 5 V
f = 0 Hz

図 5-23. CMRR vs Temperature

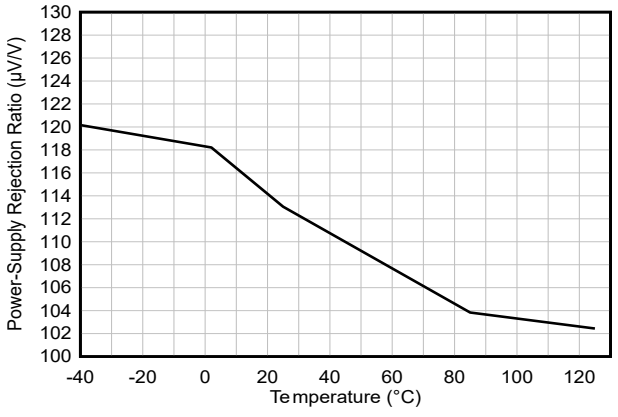


V_S = 2.7 V
f = 0 Hz

図 5-24. CMRR vs Temperature

5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)



f = 0 Hz

図 5-25. PSRR vs Temperature

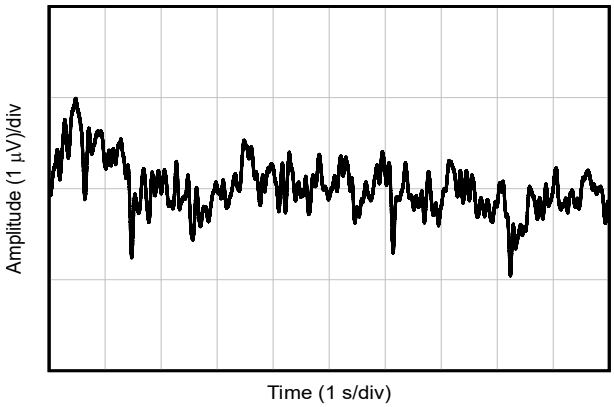


図 5-26. 0.1Hz to 10Hz Noise

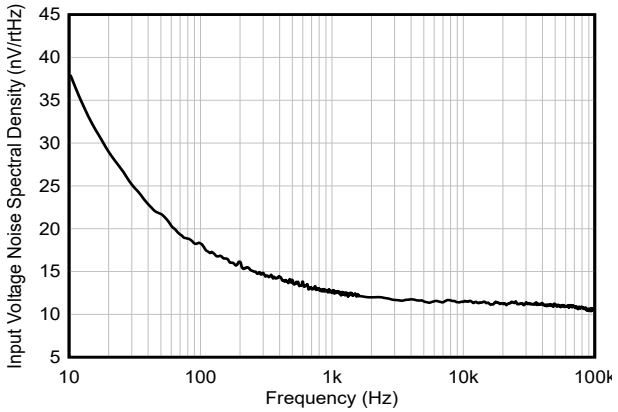
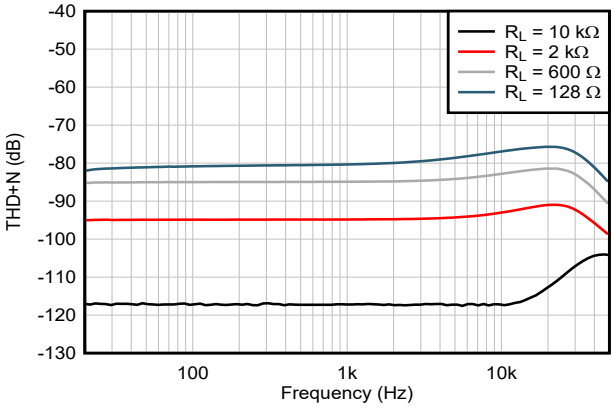
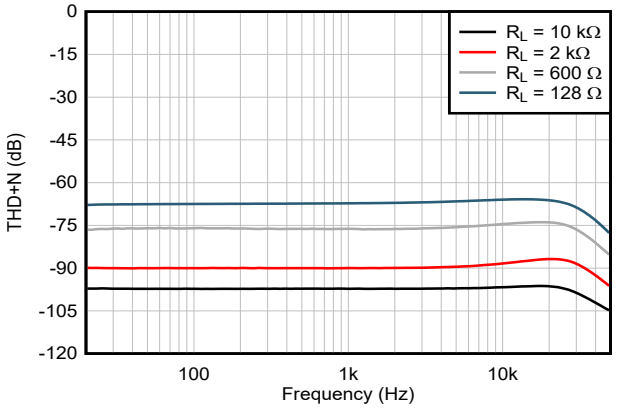


図 5-27. Input Voltage Noise Spectral Density vs Frequency



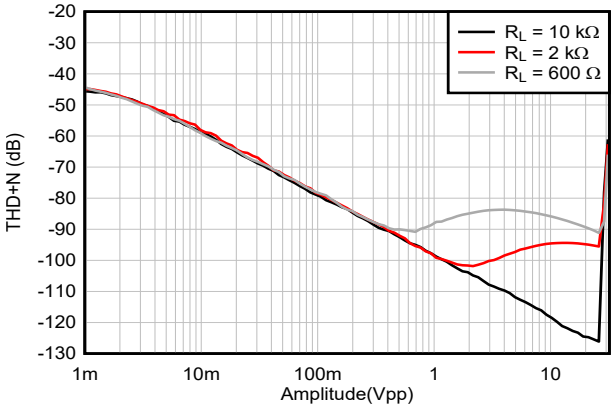
G = +1
V_{OUT} = 3 V_{RMS}
BW = 80 kHz

図 5-28. THD+N Ratio vs Frequency



G = -1
V_{OUT} = 3 V_{RMS}
BW = 80 kHz

図 5-29. THD+N Ratio vs Frequency



f = 1 kHz
BW = 80 kHz
G = +1

図 5-30. THD+N vs Output Amplitude

5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)

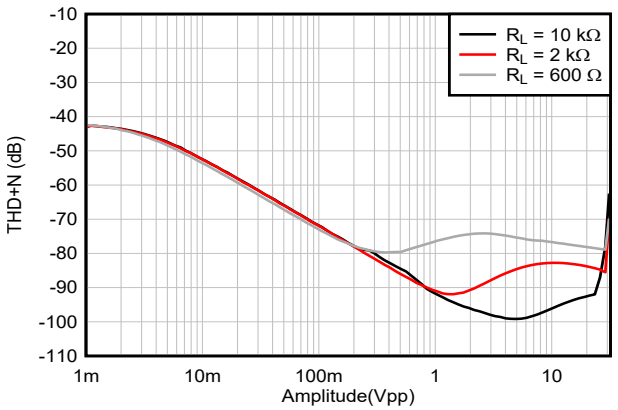


図 5-31. THD+N vs Output Amplitude

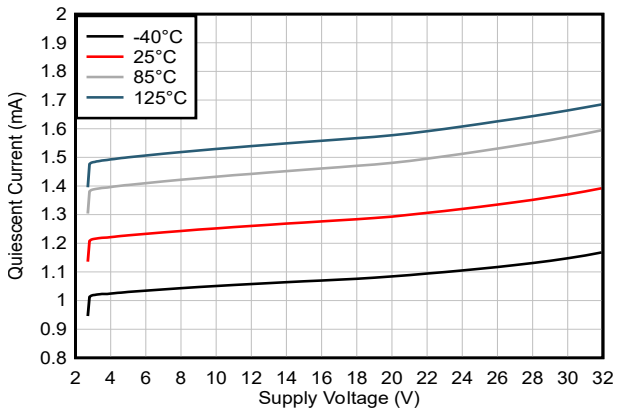


図 5-32. Quiescent Current vs Supply Voltage

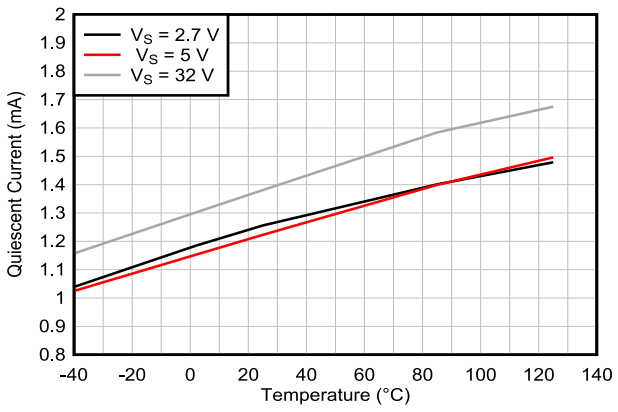


図 5-33. Quiescent Current vs Temperature

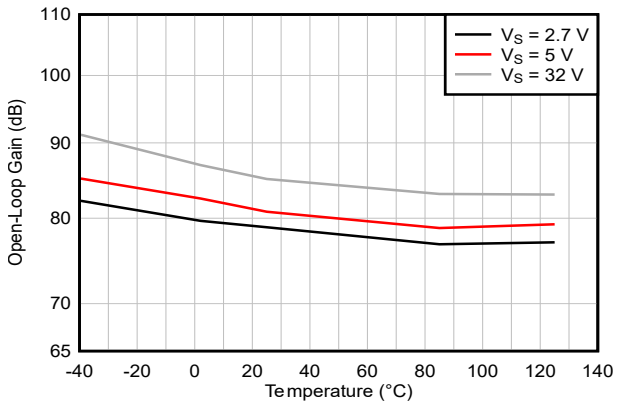


図 5-34. Open-Loop Voltage Gain vs Temperature (dB)

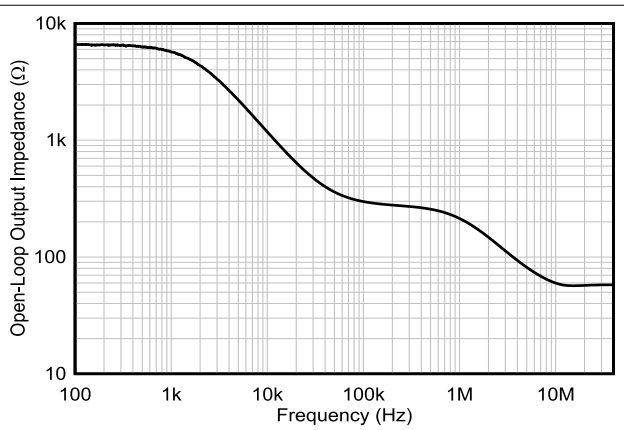


図 5-35. Open-Loop Output Impedance vs Frequency

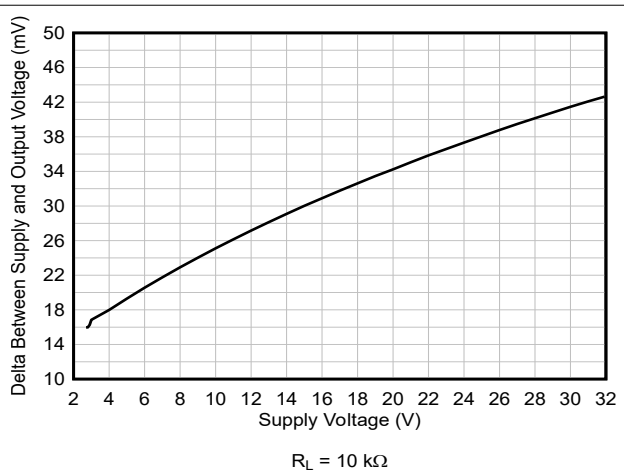
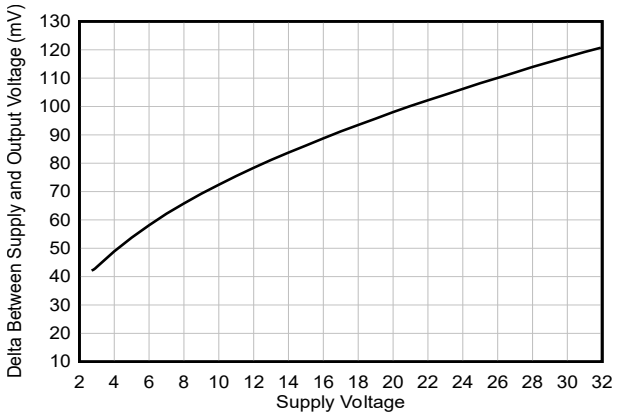


図 5-36. Output Swing vs Supply Voltage, Positive Swing

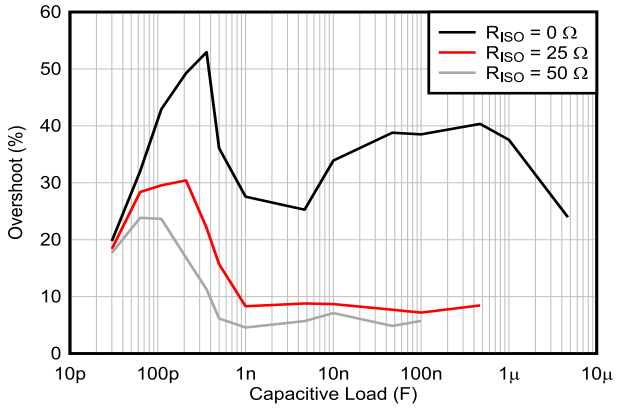
5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)



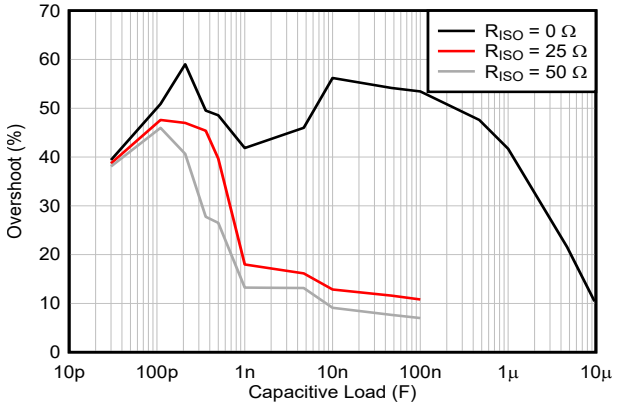
R_L = 2 kΩ

図 5-37. Output Swing vs Supply Voltage, Positive Swing



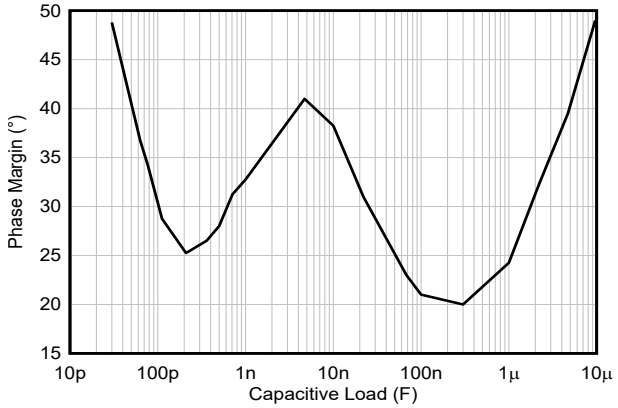
20 mV_{pp} Output Step
G = -1

図 5-38. Small-Signal Overshoot vs Capacitive Load



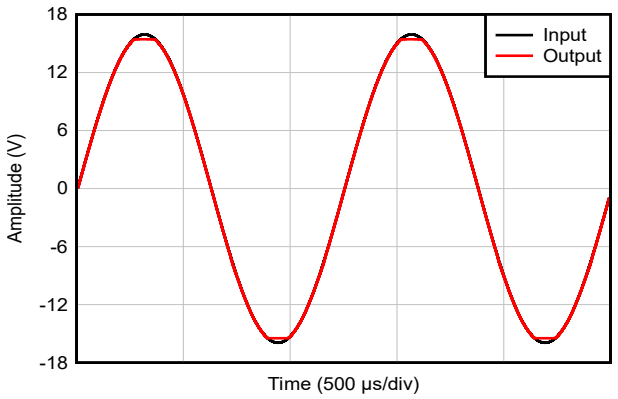
20 mV_{pp} Output Step
G = +1

図 5-39. Small-Signal Overshoot vs Capacitive Load



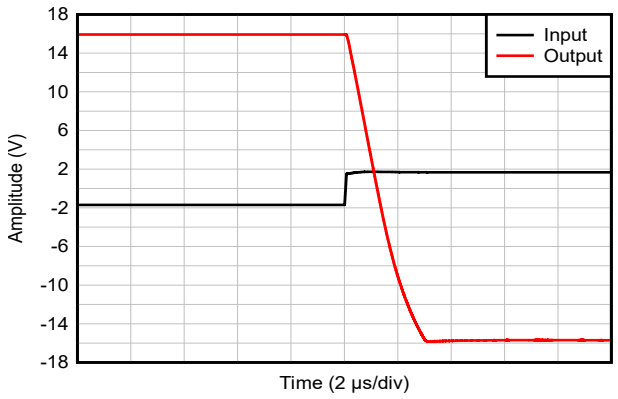
Gain = +1

図 5-40. Phase Margin vs Capacitive Load



G = 1
V_{IN} = ±16 V
V_S = V_{OUT} = ±15.5 V

図 5-41. No Phase Reversal

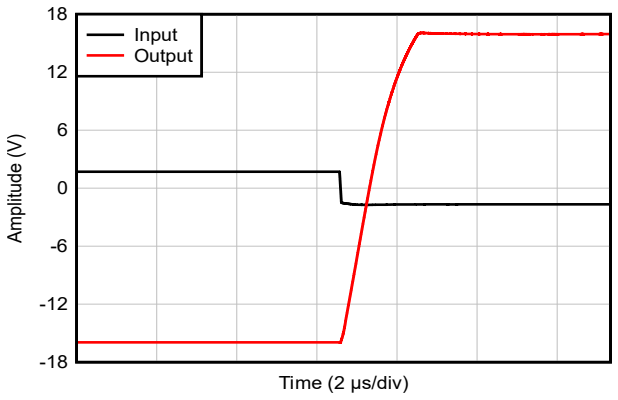


G = -10

図 5-42. Positive Overload Recovery

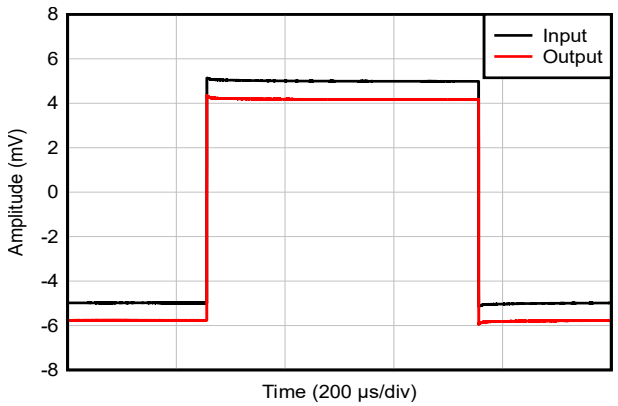
5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)



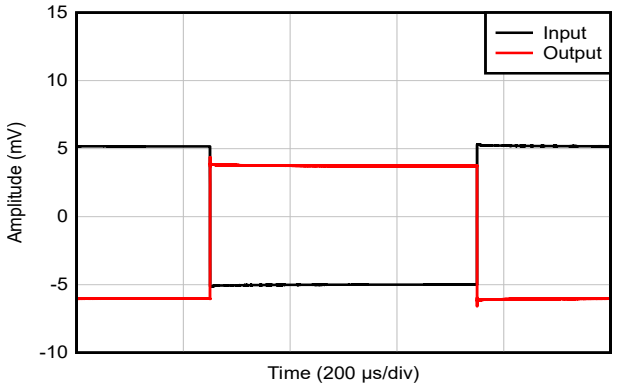
G = -10

図 5-43. Negative Overload Recovery



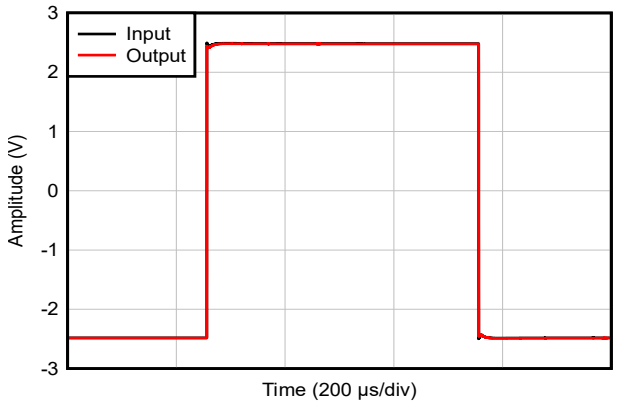
V_{IN} = 10 mV_{pp}
G = +1
C_L = 20 pF

図 5-44. Small-Signal Step Response



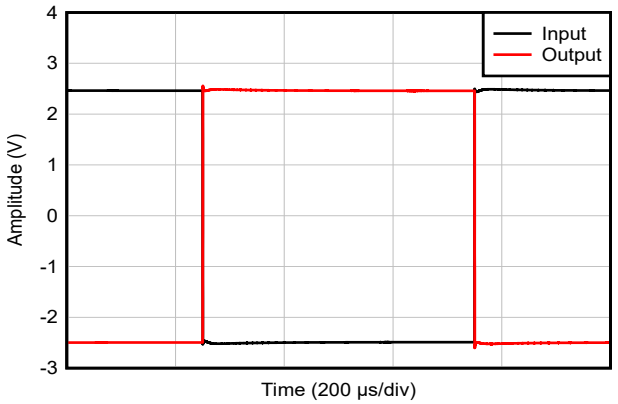
V_{IN} = 10 mV_{PP}
G = -1
C_L = 20 pF

図 5-45. Small-Signal Step Response



V_{IN} = 5 V_{pp}
G = +1
C_L = 20 pF

図 5-46. Large-Signal Step Response



V_{IN} = 5 V_{pp}
G = -1
C_L = 20 pF

図 5-47. Large-Signal Step Response

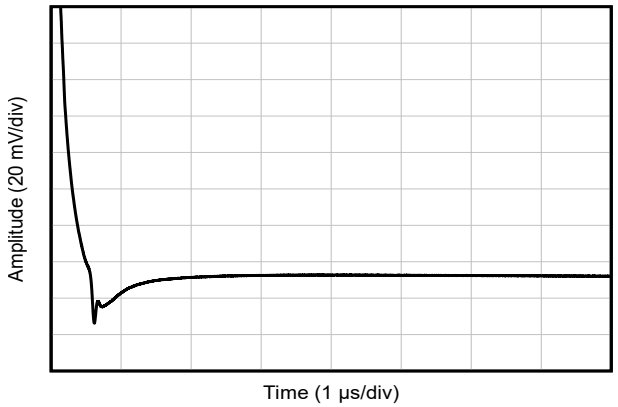


図 5-48. Settling Time

5.7 Typical Characteristics (continued)

at T_A = 25°C, V_S = ±16V, V_{CM} = V_S / 2, R_{LOAD} = 10kΩ (unless otherwise noted)

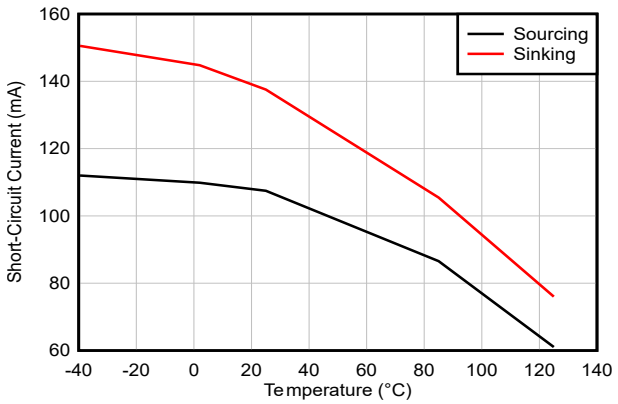


図 5-49. Short-Circuit Current vs Temperature

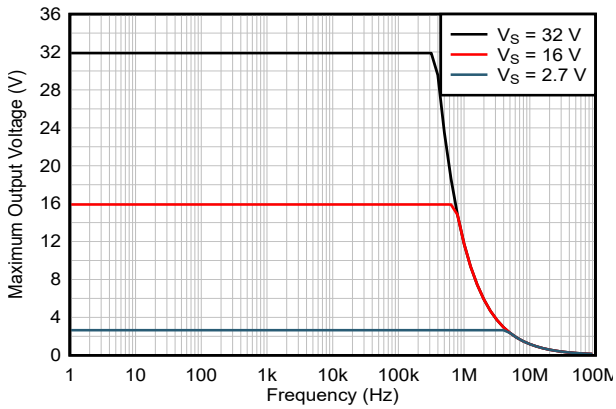


図 5-50. Maximum Output Voltage vs Frequency

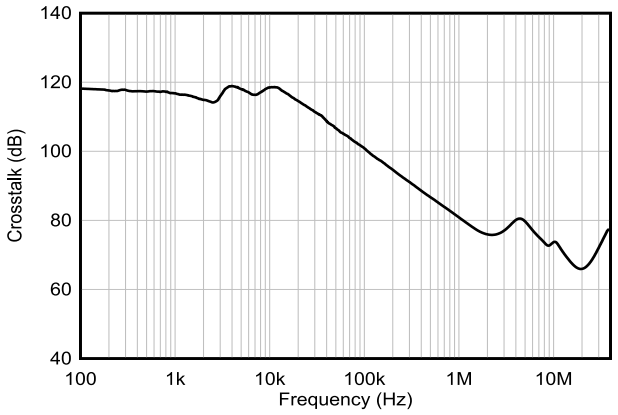


図 5-51. Channel Separation vs Frequency

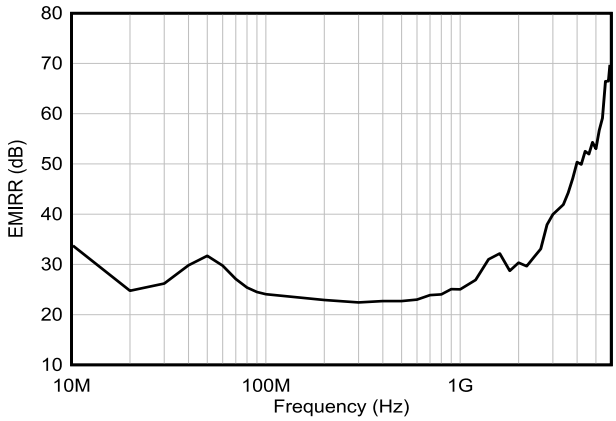


図 5-52. EMIRR (Electromagnetic Interference Rejection Ratio) vs Frequency

6 Detailed Description

6.1 Overview

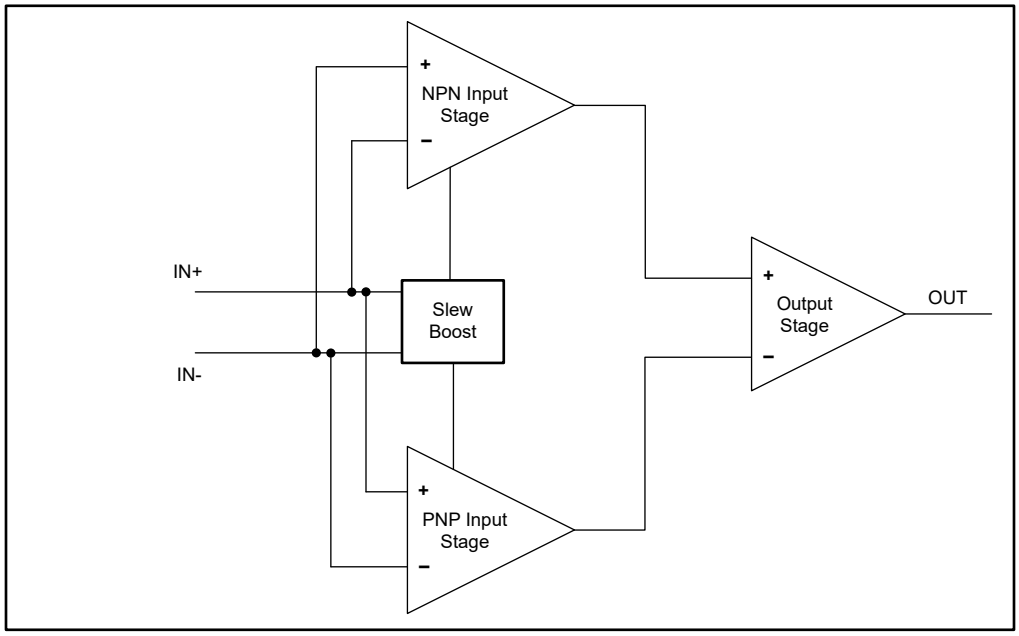
The OPAx994 family (OPA994 and OPA2994) is a family of high voltage (32V) general purpose operational amplifiers.

The OPAx994 family has a wide gain bandwidth of 24MHz when no capacitive load is present. These devices have unlimited capacitive load drive and are able to drive large capacitive loads without continuous oscillations.

These devices also offer excellent DC precision, including rail-to-rail input/output, low offset (±350µV, typical), and low offset drift (±2.5µV/°C, typical).

Special features such as unlimited capacitive load drive, high short-circuit current (±125mA, typical), and high slew rate (35V/µs, typical) make the OPAx994 an extremely flexible, robust, and high-performance operational amplifier for high-voltage industrial applications.

6.2 Functional Block Diagram



6.3 Feature Description

6.3.1 Unlimited Capacitive Load Drive

One of the challenges when designing an op amp circuit is verifying that the op amp is stable when driving capacitive loads. The OPAx994 has a unique architecture that features Unlimited Capacitive Load Drive (UCLD), which is used to prevent sustained oscillations on the output signals of the amplifier when driving large capacitive loads. This is achieved by maintaining an acceptable phase margin as the size of the capacitive load increases.

An op amp circuit that is unstable can have an unpredictable or unexpected output with poor transient performance. This typically results in large overshoots and ringing when changes occur on the input or load, but can also result in sustained oscillations. One common cause of instability in op amps can occur when connecting a load capacitor, CL, to the output of the amplifier. This instability is a result of the internal output resistance of the op amp, Zo, that creates a secondary pole with CL.

The UCLD of the OPAx994 family has a proprietary output compensation structure that is able to sense the capacitance on the output and adjust internal pole and zero structures to achieve acceptable phase margins. This behavior is unique to UCLD devices and allows the op amp to remain stable under larger capacitive loads compared to traditional amplifiers.

To keep an acceptable phase margin, UCLD devices lower the gain bandwidth product under larger capacitive loads. The OPAx994 is specified to have a gain bandwidth product of 24MHz without significant capacitive load, but this value will begin to decrease at the point where a traditional amplifier would begin to become unstable. This tradeoff is what extends the output drive capability. OPAx994 is designed with a wide gain bandwidth product to make sure there is headroom for many general-purpose applications with higher capacitive loads.

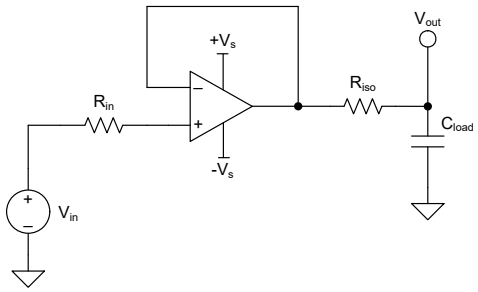


図 6-1. Extending Capacitive Load Drive With the OPA994

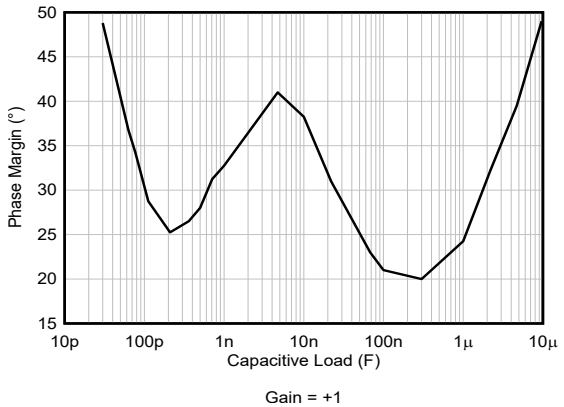


図 6-2. Phase Margin vs Capacitive Load

6.3.2 Common-Mode Voltage Range

The OPAx994 is a 32V, true rail-to-rail input operational amplifier with an input common-mode range that extends to both supply rails. This wide range is achieved with paralleled complementary PNP and NPN differential input pairs, as shown in 図 6-3. The NPN pair is active for input voltages close to the positive rail, typically from (V+) – 1V to the positive supply. The PNP pair is active for inputs from the negative supply to approximately (V+) – 2V. There is a small transition region, typically (V+) – 2V to (V+) – 1V, in which both input pairs are on. This transition region can vary modestly with process variation. Within this region PSRR, CMRR, offset voltage, offset drift, noise, and THD performance can be degraded compared to operation outside this region.

For more information on common-mode voltage range and complementary pair interaction, see *Op Amps With Complementary-Pair Input Stages* application note.

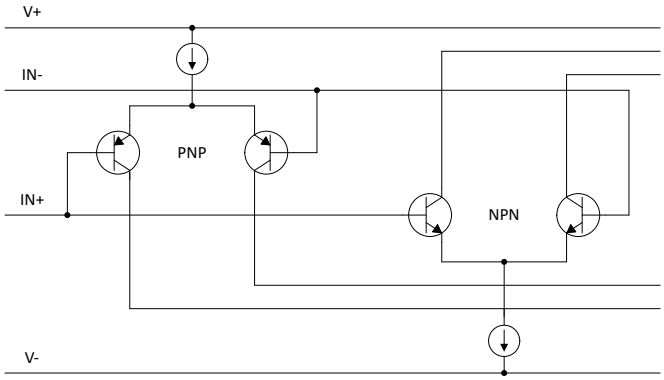


図 6-3. Rail-to-Rail Input Stage

6.3.3 Phase Reversal Protection

The OPAx994 family has internal phase-reversal protection. Many op amps exhibit a phase reversal when the input is driven beyond the linear common-mode range. This condition is most often encountered in non-inverting circuits when the input is driven beyond the specified common-mode voltage range, causing the output to reverse into the opposite rail. The OPAx994 is a rail-to-rail input op amp; therefore, the common-mode range can extend up to the rails. Input signals beyond the rails do not cause phase reversal; instead, the output limits into the appropriate rail. This performance is shown in 図 6-4. For more information on phase reversal, see *Op Amps With Complementary-Pair Input Stages* application note.

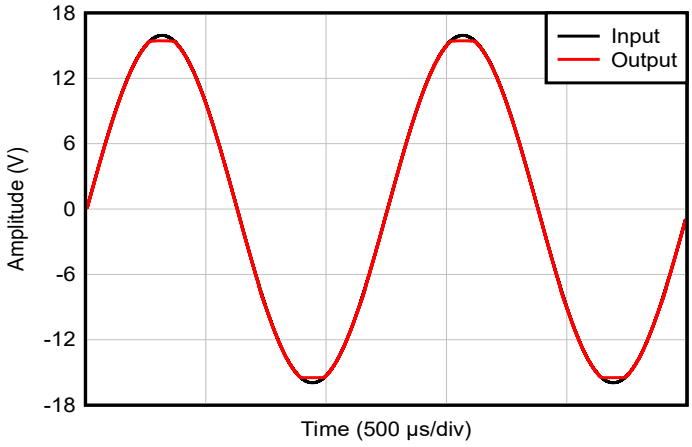


図 6-4. No Phase Reversal

6.3.4 Electrical Overstress

Designers often ask questions about the capability of an operational amplifier to withstand electrical overstress (EOS). These questions tend to focus on the device inputs, but can involve the supply voltage pins or even the output pin. Each of these different pin functions have electrical stress limits determined by the voltage breakdown characteristics of the particular semiconductor fabrication process and specific circuits connected to the pin. Additionally, internal electrostatic discharge (ESD) protection is built into these circuits to protect them from accidental ESD events both before and during product assembly.

It is helpful to have a good understanding of this basic ESD circuitry and its relevance to an electrical overstress event. 図 6-5 shows an illustration of the ESD circuits contained in the OPAx994 (indicated by the dashed line area). The ESD protection circuitry involves several current-steering diodes connected from the input and output pins and routed back to the internal power-supply lines, where the diodes meet at an absorption device or the power-supply ESD cell, internal to the operational amplifier. This protection circuitry is intended to remain inactive during normal circuit operation.

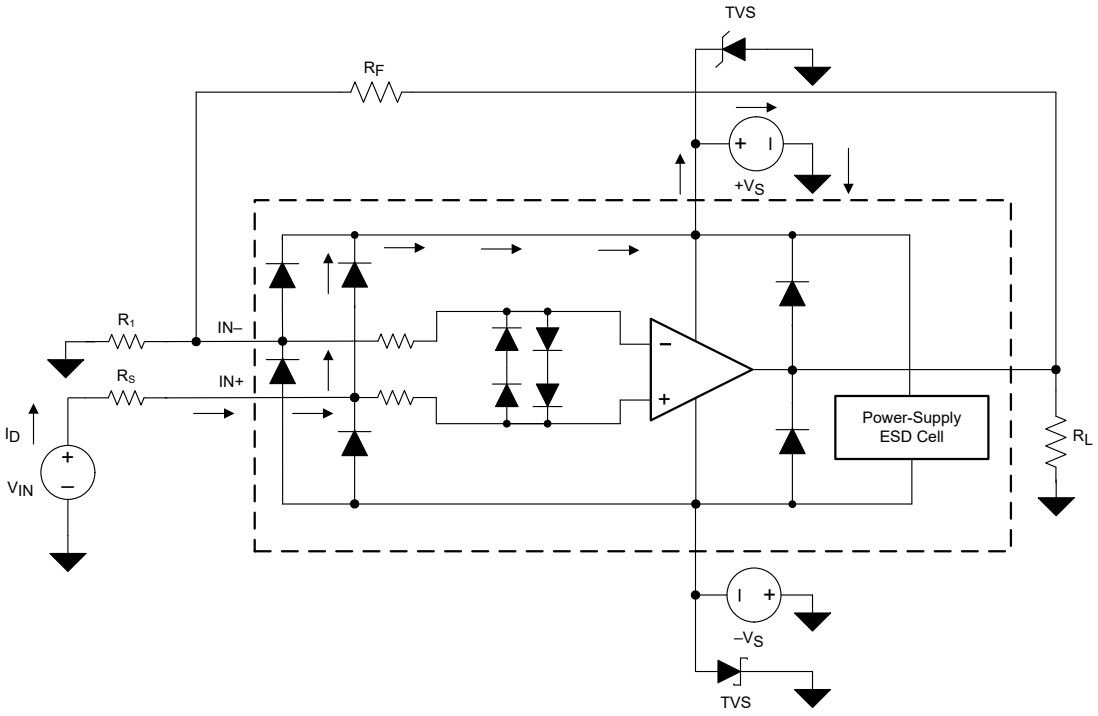


図 6-5. Equivalent Internal ESD Circuitry Relative to a Typical Circuit Application

An ESD event produces a short-duration, high-voltage pulse that is transformed into a short-duration, high-current pulse while discharging through a semiconductor device. The ESD protection circuits are designed to provide a current path around the operational amplifier core to prevent damage. The energy absorbed by the protection circuitry is then dissipated as heat.

When an ESD voltage develops across two or more amplifier device terminals, current flows through one or more steering diodes. Depending on the path that the current takes, the absorption device can activate. The absorption device has a trigger, or threshold voltage, that is above the normal operating voltage of the OPAx994 but below the device breakdown voltage level. When this threshold is exceeded, the absorption device quickly activates and clamps the voltage across the supply rails to a safe level.

When the operational amplifier connects into a circuit (as shown in 図 6-5), the ESD protection components are intended to remain inactive and do not become involved in the application circuit operation. However, circumstances can arise where an applied voltage exceeds the operating voltage range of a given terminal. If this condition occurs, there is a risk that some internal ESD protection circuits can turn on and conduct current. Any such current flow occurs through steering-diode paths and rarely involves the absorption device.

図 6-5 shows a specific example where the input voltage (V_{IN}) exceeds the positive supply voltage ($+V_S$) by 500mV or more. Much of what happens in the circuit depends on the supply characteristics. If $+V_S$ can sink the current, one of the upper input steering diodes conducts and directs current to $+V_S$. Excessively high current levels can flow with increasingly higher V_{IN}. As a result, the data sheet specifications recommend that applications limit the input current to 10mA.

If the supply is not capable of sinking the current, V_{IN} can begin sourcing current to the operational amplifier, and then take over as the source of positive supply voltage. The danger in this case is that the voltage can rise to levels that exceed the operational amplifier absolute maximum ratings.

Another common question involves what happens to the amplifier if an input signal is applied to the input while the power supplies $+V_S$ or $–V_S$ are at 0V. Again, this question depends on the supply characteristic while at 0V, or at a level below the input-signal amplitude. If the supplies appear as high impedance, then the input source supplies the operational amplifier current through the current-steering diodes. This state is not a normal bias condition; most likely, the amplifier will not operate normally. If the supplies are low impedance, then the current through the steering diodes can become quite high. The current level depends on the ability of the input source to deliver current, and any resistance in the input path.

If there is any uncertainty about the ability of the supply to absorb this current, add external Zener diodes to the supply terminals; see 図 6-5. Select the Zener voltage so that the diode does not turn on during normal operation. However, the Zener voltage must be low enough so that the Zener diode conducts if the supply terminal begins to rise above the safe-operating, supply-voltage level.

The OPAx994 input terminals are protected from excessive differential voltage with back-to-back diodes; see 図 6-5. In most circuit applications, the input protection circuitry has no effect. However, in low-gain or G = 1 circuits, fast-ramping input signals can forward-bias these diodes because the output of the amplifier cannot respond rapidly enough to the input ramp. If the input signal is fast enough to create this forward-bias condition, limit the input signal current to 10mA or less. If the input signal current is not inherently limited, an input series resistor can be used to limit the input signal current. This input series resistor degrades the low-noise performance of the OPAx994. 図 6-5 shows an example configuration that implements a current-limiting feedback resistor.

6.3.5 Overload Recovery

Overload recovery is defined as the time required for the op amp output to recover from a saturated state to a linear state. The output devices of the op amp enter a saturation region when the output voltage exceeds the rated operating voltage, either due to the high input voltage or the high gain. After the device enters the saturation region, the charge carriers in the output devices require time to return back to the linear state. After the charge carriers return back to the linear state, the device begins to slew at the specified slew rate. Thus, the

propagation delay in case of an overload condition is the sum of the overload recovery time and the slew time. The overload recovery time for the OPAx994 is approximately 130ns.

6.3.6 Typical Specifications and Distributions

Designers often have questions about a typical specification of an amplifier to design a more robust circuit. Due to natural variation in process technology and manufacturing procedures, every specification of an amplifier can exhibit some amount of deviation from the ideal value, like the input offset voltage of an amplifier. These deviations often follow *Gaussian* (*bell curve*), or *normal* distributions, and circuit designers can leverage this information to guardband their system, even when there is not a minimum or maximum specification in the *Electrical Characteristics* table.

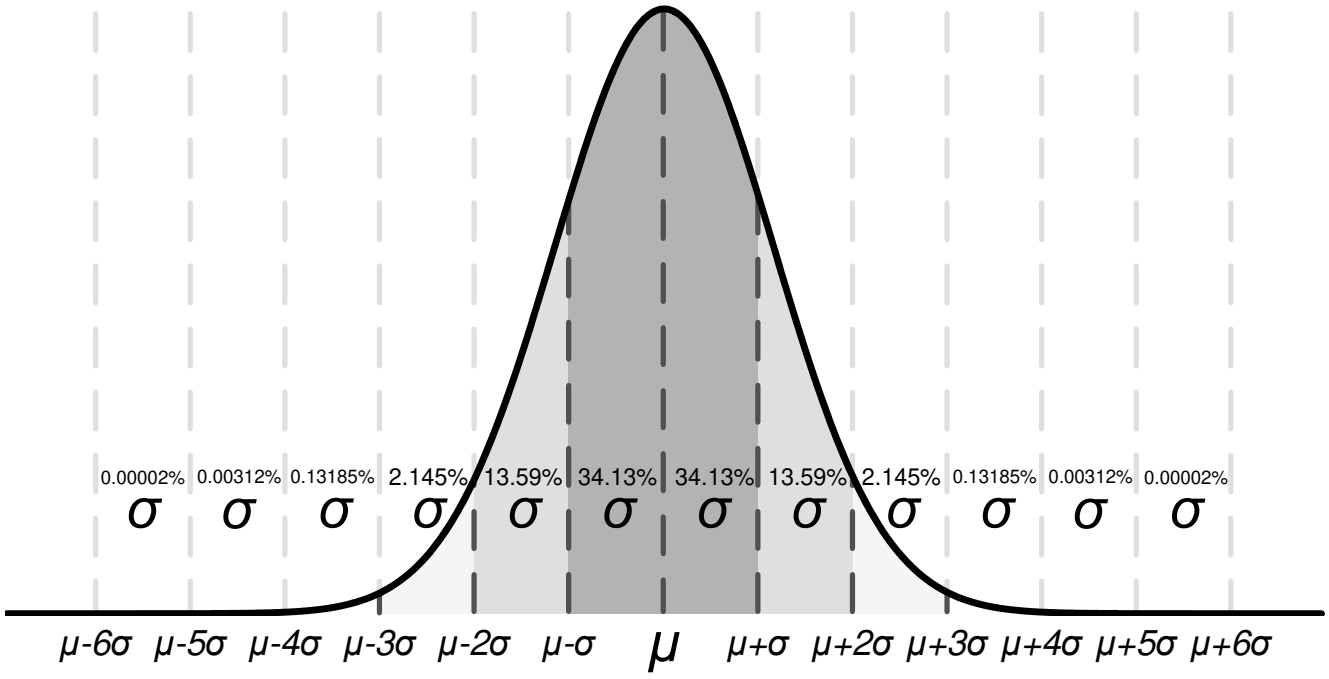


図 6-6. Ideal Gaussian Distribution

The 図 6-6 figure shows an example distribution, where *μ*, or *mu*, is the mean of the distribution, and where *σ*, or *sigma*, is the standard deviation of a system. For a specification that exhibits this kind of distribution, approximately two-thirds (68.26%) of all units can be expected to have a value within one standard deviation, or one sigma, of the mean (from *μ–σ* to *μ+σ*).

Depending on the specification, values listed in the *typical* column of the *Electrical Characteristics* table are represented in different ways. As a general rule, if a specification naturally has a nonzero mean (for example, like gain bandwidth), then the typical value is equal to the mean (μ). However, if a specification naturally has a mean near zero (like input offset voltage), then the typical value is equal to the mean plus one standard deviation (μ + σ) to most accurately represent the typical value.

Designers can use this chart to calculate approximate probability of a specification in a unit; for example, for OPAx994, the typical input voltage offset is 350μV. So 68.2% of all OPAx994 devices are expected to have an offset from –350μV to +350μV. At 4 *σ* (±800μV), 99.9937% of the distribution has an offset voltage less than ±1400μV, which means 0.0063% of the population is outside of these limits, which corresponds to about 1 in 15,873 units.

Specifications with a value in the minimum or maximum column are tested by TI, unless otherwise noted, and units outside these limits are removed from production material. For example, the OPAx994 family has a maximum offset voltage of 2.3mV at 25°C, and even though this is extremely unlikely, units with larger offset than 2.3mV are removed from production material.

For specifications with no value in the minimum or maximum column, consider selecting a sigma value of sufficient guardband for the designers application, and design worst-case conditions using this value. For example, the 6σ value corresponds to about 1 in 500 million units, which is an extremely unlikely chance, and can be an option as a wide guardband to design a system around. In this case, the OPAx994 family does not have a maximum or minimum for offset voltage drift. But based on the typical value of 2.5µV/°C in the *Electrical Characteristics* table, it can be calculated that the 6σ value for offset voltage drift is about 15µV/°C. When designing for worst-case system conditions, this value can be used to estimate the worst possible offset across temperature without having an actual minimum or maximum value.

Note that process variation and adjustments over time can shift typical means and standard deviations, and unless there is a value in the minimum or maximum specification column, TI cannot assure the performance of a device. Only use this information to estimate the performance of a device.

6.4 Device Functional Modes

The OPAx994 has a single functional mode and is operational when the power-supply voltage is greater than or equal to 2.7V (±1.35V). The maximum power supply voltage for the OPAx994 is 32V (±16V).

7 Application and Implementation

注

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

7.1 Application Information

The OPAx994 family offers excellent DC precision and AC performance. These devices operate up to 32V supply rails and offer true rail-to-rail input/output, low offset voltage and offset voltage drift, as well as 24MHz bandwidth and high output drive. These features make the OPAx994 a robust, high-performance operational amplifier for high-voltage industrial applications.

7.2 Typical Applications

7.2.1 Low-Side Current Measurement

図 7-1 shows the OPA994 configured in a low-side current sensing application. For a full analysis of the circuit shown in 図 7-1 including theory, calculations, simulations, and measured data, see TI Precision Design TIPD129, *0A to 1A Single-Supply Low-Side Current-Sensing Solution*.

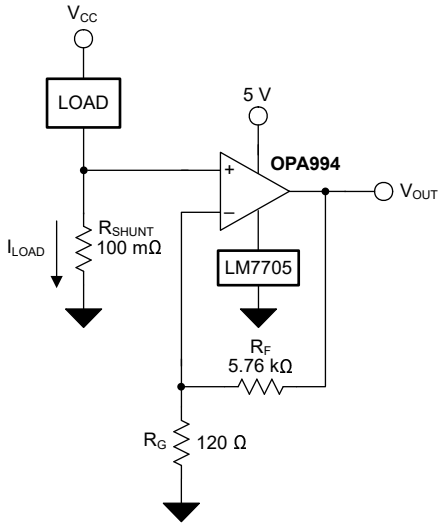


図 7-1. OPAx994 in a Low-Side, Current-Sensing Application

7.2.1.1 Design Requirements

The design requirements for this design are as follows:

- Load current: 0A to 1A
- Max output voltage: 4.9V
- Maximum shunt voltage: 100mV

7.2.1.2 Detailed Design Procedure

The transfer function of the circuit in 図 7-1 is given in 式 1:

$$V_{OUT} = I_{LOAD} \times R_{SHUNT} \times Gain \quad (1)$$

The load current (I_{LOAD}) produces a voltage drop across the shunt resistor (R_{SHUNT}). The load current is set from 0A to 1A. To keep the shunt voltage below 100mV at maximum load current, the largest shunt resistor is defined using 式 2:

$$R_{SHUNT} = \frac{V_{SHUNT\_MAX}}{I_{LOAD\_MAX}} = \frac{100mV}{1A} = 100m\Omega \quad (2)$$

Using 式 2, R_{SHUNT} is calculated to be 100mΩ. The voltage drop produced by I_{LOAD} and R_{SHUNT} is amplified by the OPA994 to produce an output voltage of 0V to 4.9V. The gain needed by the OPA994 to produce the necessary output voltage is calculated using 式 3:

$$Gain = \frac{(V_{OUT\_MAX} - V_{OUT\_MIN})}{(V_{IN\_MAX} - V_{IN\_MIN})} \quad (3)$$

Using 式 3, the required gain is calculated to be 49V/V, which is set with resistors R_F and R_G. 式 4 is used to size the resistors, R_F and R_G, to set the gain of the OPA994 to 49V/V.

$$Gain = 1 + \frac{(R_F)}{(R_G)} \quad (4)$$

Choosing R_F as 5.76kΩ, R_G is calculated to be 120Ω. R_F and R_G were chosen as 5.76kΩ and 120Ω because they are standard value resistors that create a 49:1 ratio. Other resistors that create a 49:1 ratio can also be used. However, excessively large resistors can generate thermal noise that exceeds the intrinsic noise of the op amp. 図 7-2 shows the measured transfer function of the circuit shown in 図 7-1.

7.2.1.3 Application Curve

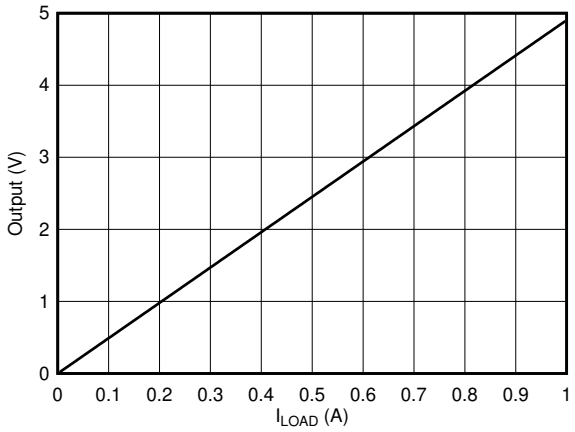


図 7-2. Low-Side, Current-Sense, Transfer Function

7.3 Power Supply Recommendations

The OPAx994 is specified for operation from 2.7V to 32V (±1.35V to ±16V); many specifications apply from –40°C to 125°C or with specific supply voltages and test conditions.

> **注意**
>
> Supply voltages larger than 33V can permanently damage the device; see *Absolute Maximum Ratings*.

Place 0.1µF bypass capacitors close to the power-supply pins to reduce errors coupling in from noisy or high-impedance power supplies. For more detailed information on bypass capacitor placement, refer to *Layout*.

7.4 Layout

7.4.1 Layout Guidelines

For best operational performance of the device, use good PCB layout practices, including:

- Noise can propagate into analog circuitry through the power pins of the circuit as a whole and op amp itself. Bypass capacitors are used to reduce the coupled noise by providing low-impedance power sources local to the analog circuitry.
  - Connect low-ESR, 0.1µF ceramic bypass capacitors between each supply pin and ground, placed as close to the device as possible. A single bypass capacitor from V+ to ground is applicable for single-supply applications.
- Separate grounding for analog and digital portions of circuitry is one of the simplest and most-effective methods of noise suppression. One or more layers on multilayer PCBs are usually devoted to ground planes. A ground plane helps distribute heat and reduces EMI noise pickup. Make sure to physically separate digital and analog grounds paying attention to the flow of the ground current.
- To reduce parasitic coupling, run the input traces as far away from the supply or output traces as possible. If these traces cannot be kept separate, crossing the sensitive trace perpendicular is much better as opposed to in parallel with the noisy trace.
- Place the external components as close to the device as possible. As shown in 図 7-4, keeping RF and RG close to the inverting input minimizes parasitic capacitance.
- Keep the length of input traces as short as possible. Always remember that the input traces are the most sensitive part of the circuit.
- Consider a driven, low-impedance guard ring around the critical traces. A guard ring can significantly reduce leakage currents from nearby traces that are at different potentials.
- Cleaning the PCB following board assembly is recommended for best performance.
- Any precision integrated circuit can experience performance shifts due to moisture ingress into the plastic package. Following any aqueous PCB cleaning process, baking the PCB assembly is recommended to remove moisture introduced into the device packaging during the cleaning process. A low temperature, post cleaning bake at 85°C for 30 minutes is sufficient for most circumstances.

7.4.2 Layout Example

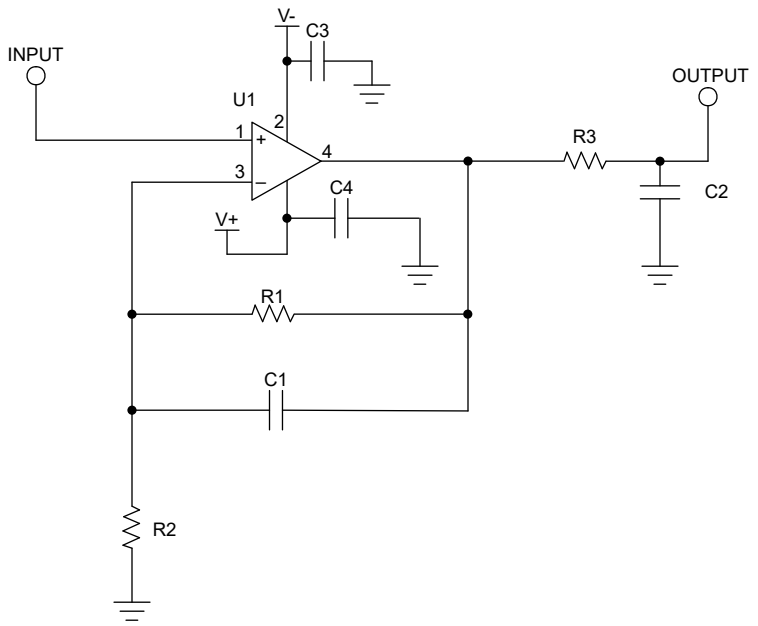


図 7-3. Schematic for Noninverting Configuration Layout Example

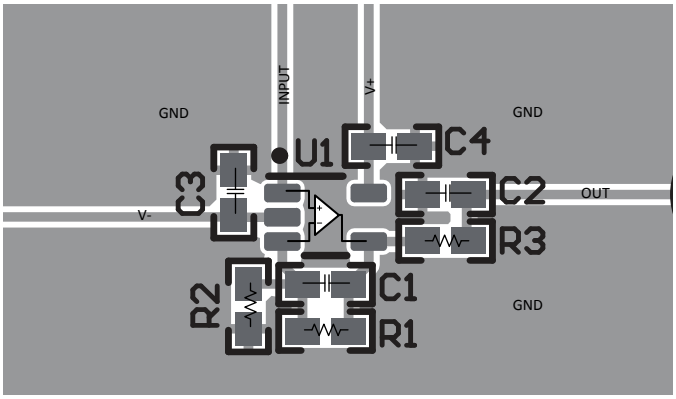


図 7-4. Example Layout for SC70 (DCK) Package

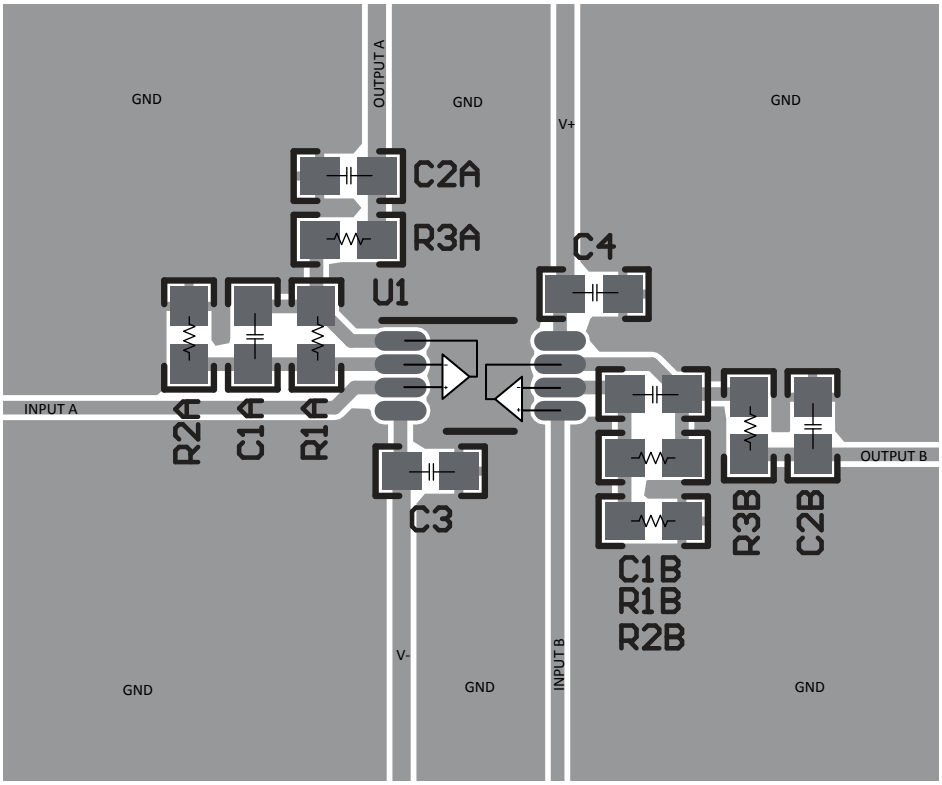


図 7-5. Example Layout for VSSOP-8 (DGK) Package

8 Device and Documentation Support

8.1 Device Support

8.1.1 Development Support

8.1.1.1 TINA-TI™ (Free Software Download)

TINA™ is a simple, powerful, and easy-to-use circuit simulation program based on a SPICE engine. TINA-TI is a free, fully-functional version of the TINA software, preloaded with a library of macro models in addition to a range of both passive and active models. TINA-TI provides all the conventional dc, transient, and frequency domain analysis of SPICE, as well as additional design capabilities.

Available as a free download from the Analog eLab Design Center, TINA-TI offers extensive post-processing capability that allows users to format results in a variety of ways. Virtual instruments offer the ability to select input waveforms and probe circuit nodes, voltages, and waveforms, creating a dynamic quick-start tool.

注

These files require that either the TINA software (from DesignSoft™) or TINA-TI software be installed. Download the free TINA-TI software from the TINA-TI folder.

8.2 Documentation Support

8.2.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *EMI Rejection Ratio of Operational Amplifiers* application note
- Texas Instruments, *Op Amps With Complementary-Pair Input Stages* application note
- Texas Instruments, *0A to 1A, Single-Supply, Low-Side, Current Sensing Solution* design guide

8.3 ドキュメントの更新通知を受け取る方法

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8.7 用語集

テキサス・インスツルメンツ用語集　この用語集には、用語や略語の一覧および定義が記載されています。

9 Revision History

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

Changes from Revision C (September 2024) to Revision D (November 2024)	Page
• データシート全体に OPA2994IDDFR (SOT-23-8) をアクティブのステータスで追加	1

Changes from Revision B (March 2024) to Revision C (September 2024)	Page
• OPA994IDBVR (SOT-23-5) および OPA994IDCKR (SC70-5) のステータスをプレビューからアクティブに変更	1

Changes from Revision A (November 2023) to Revision B (March 2024)	Page
• 「概要」セクションのスルーレートを変更：18V/µs から 35V/µs	1
• OPA2994IDGKR のステータスをプレビューからアクティブに変更	1
• Changed Human Body Model (HBM) ESD rating from 2.5kV to 4kV	5
• Added the DGK (VSSOP) thermal values to the Thermal Information for Dual Channel table	6

Changes from Revision * (June 2023) to Revision A (November 2023)	Page
• データシート全体にわたって最大電源電圧を 24V から 32V に更新	1
• OPA2994IDR のステータスをプレビューからアクティブに変更	1
• OPA994 の SOIC-8 パッケージ情報を追加	1
• Added device typical characteristic curves in *Typical Characteristics* section	9

10 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
OPA2994IDDFR	Active	Production	SOT-23-THIN (DDF) | 8	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	O2994
OPA2994IDDFR.B	Active	Production	SOT-23-THIN (DDF) | 8	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	O2994
OPA2994IDGKR	Active	Production	VSSOP (DGK) | 8	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	O994
OPA2994IDGKR.B	Active	Production	VSSOP (DGK) | 8	2500 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	O994
OPA2994IDR	Active	Production	SOIC (D) | 8	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	O2994I
OPA2994IDR.B	Active	Production	SOIC (D) | 8	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	O2994I
OPA994IDBVR	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	OPDBV
OPA994IDBVR.B	Active	Production	SOT-23 (DBV) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	OPDBV
OPA994IDCKR	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	994
OPA994IDCKR.B	Active	Production	SC70 (DCK) | 5	3000 | LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	994
OPA994IDR	Active	Production	SOIC (D) | 8	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	O994I
OPA994IDR.B	Active	Production	SOIC (D) | 8	3000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	O994I

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

OTHER QUALIFIED VERSIONS OF OPA2994, OPA994 :

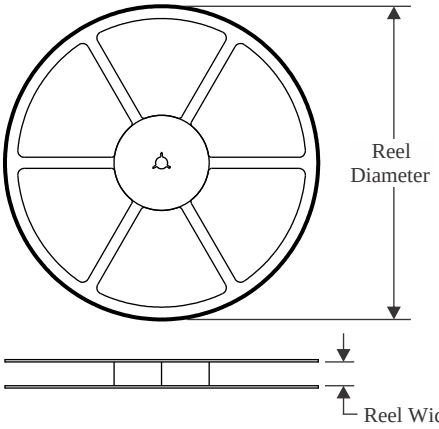
- Automotive : OPA2994-Q1, OPA994-Q1

NOTE: Qualified Version Definitions:

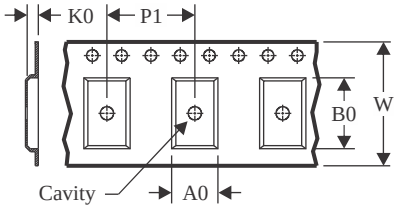
- Automotive - Q100 devices qualified for high-reliability automotive applications targeting zero defects

TAPE AND REEL INFORMATION

REEL DIMENSIONS

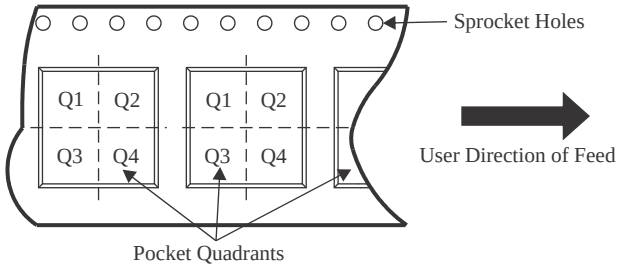


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

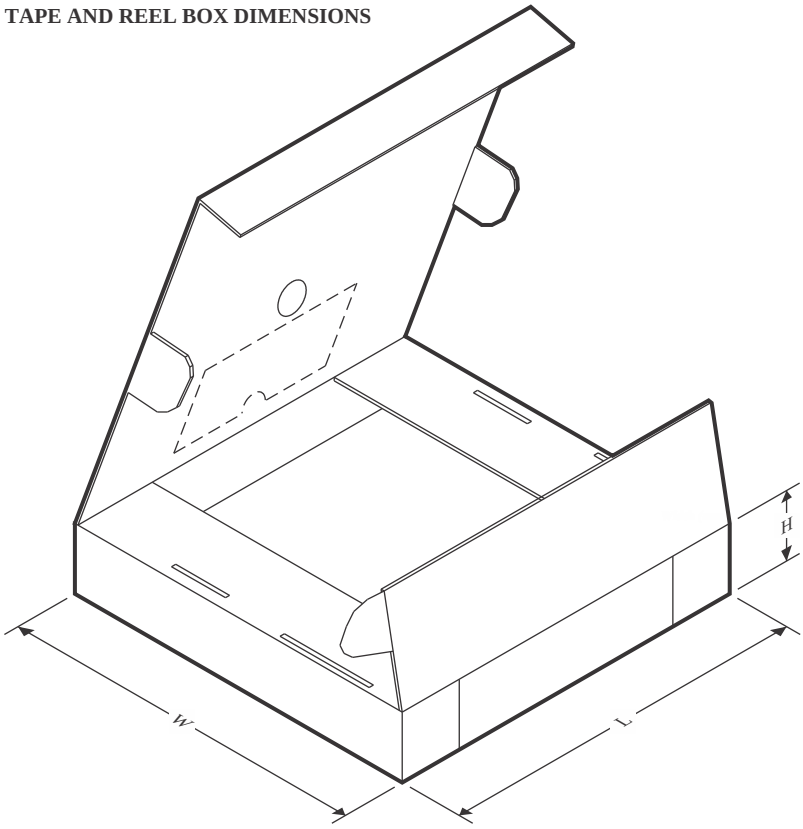
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
OPA2994IDDFR	SOT-23-THIN	DDF	8	3000	180.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
OPA2994IDGKR	VSSOP	DGK	8	2500	330.0	12.4	5.25	3.35	1.25	8.0	12.0	Q1
OPA2994IDR	SOIC	D	8	3000	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
OPA994IDBVR	SOT-23	DBV	5	3000	178.0	8.4	3.2	3.2	1.4	4.0	8.0	Q3
OPA994IDCKR	SC70	DCK	5	3000	180.0	8.4	2.3	2.5	1.2	4.0	8.0	Q3
OPA994IDR	SOIC	D	8	3000	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

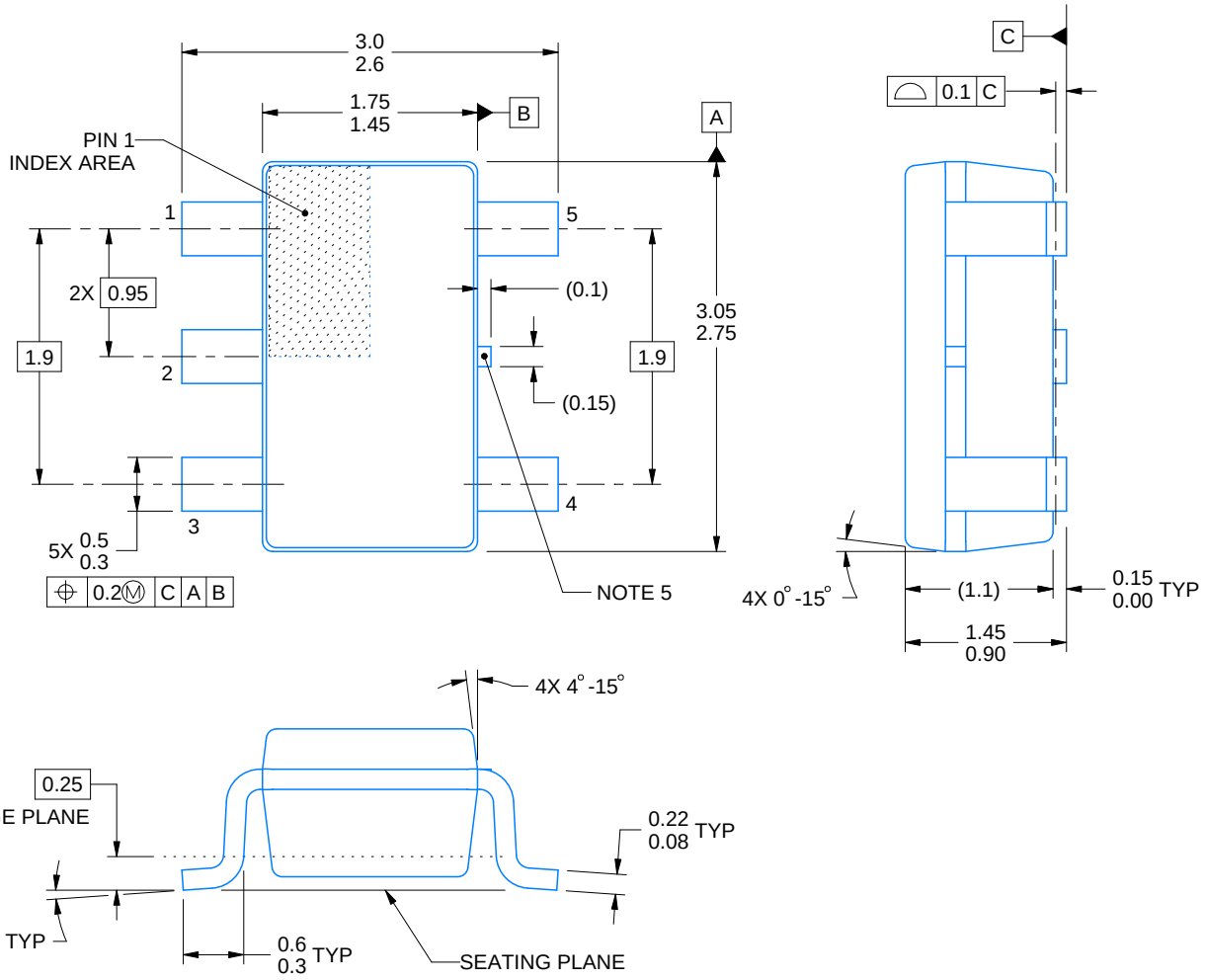
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
OPA2994IDDFR	SOT-23-THIN	DDF	8	3000	210.0	185.0	35.0
OPA2994IDGKR	VSSOP	DGK	8	2500	366.0	364.0	50.0
OPA2994IDR	SOIC	D	8	3000	353.0	353.0	32.0
OPA994IDBVR	SOT-23	DBV	5	3000	208.0	191.0	35.0
OPA994IDCKR	SC70	DCK	5	3000	210.0	185.0	35.0
OPA994IDR	SOIC	D	8	3000	353.0	353.0	32.0

PACKAGE OUTLINE

DBV0005A

SOT-23 - 1.45 mm max height

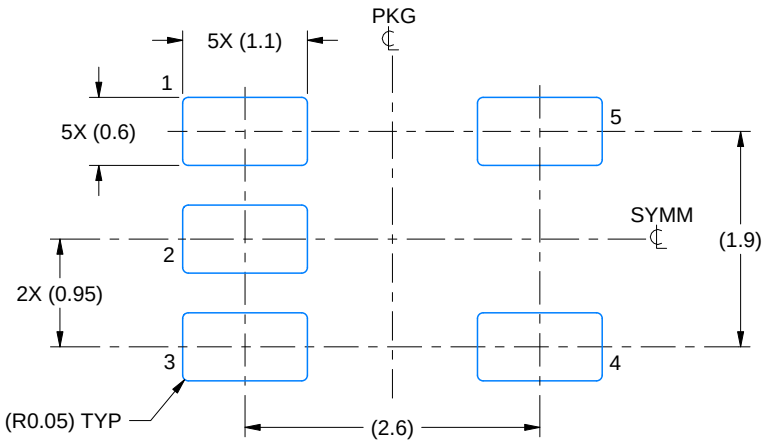
SMALL OUTLINE TRANSISTOR



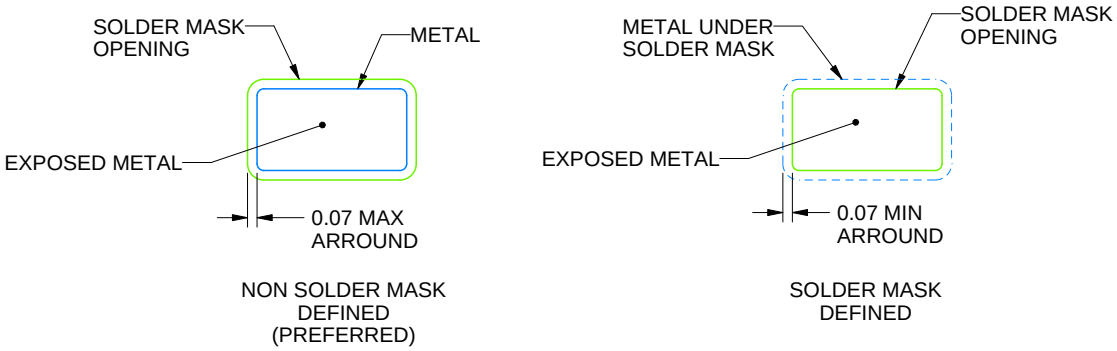
4214839/K 08/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-178.
4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
5. Support pin may differ or may not be present.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X

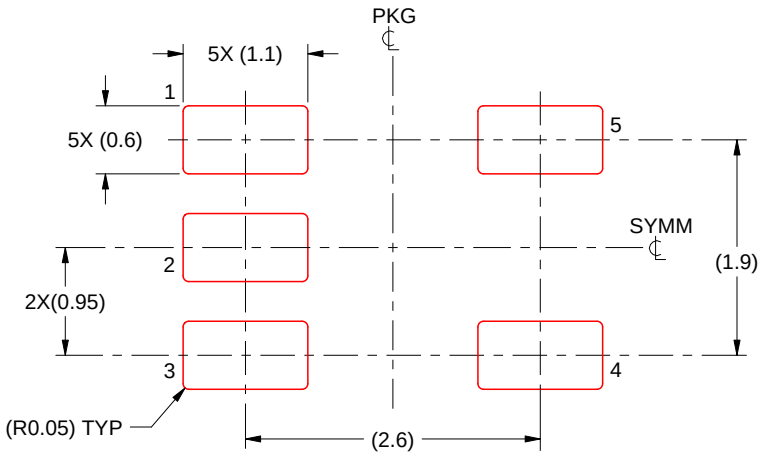


SOLDER MASK DETAILS

4214839/K 08/2024

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4214839/K 08/2024

NOTES: (continued)

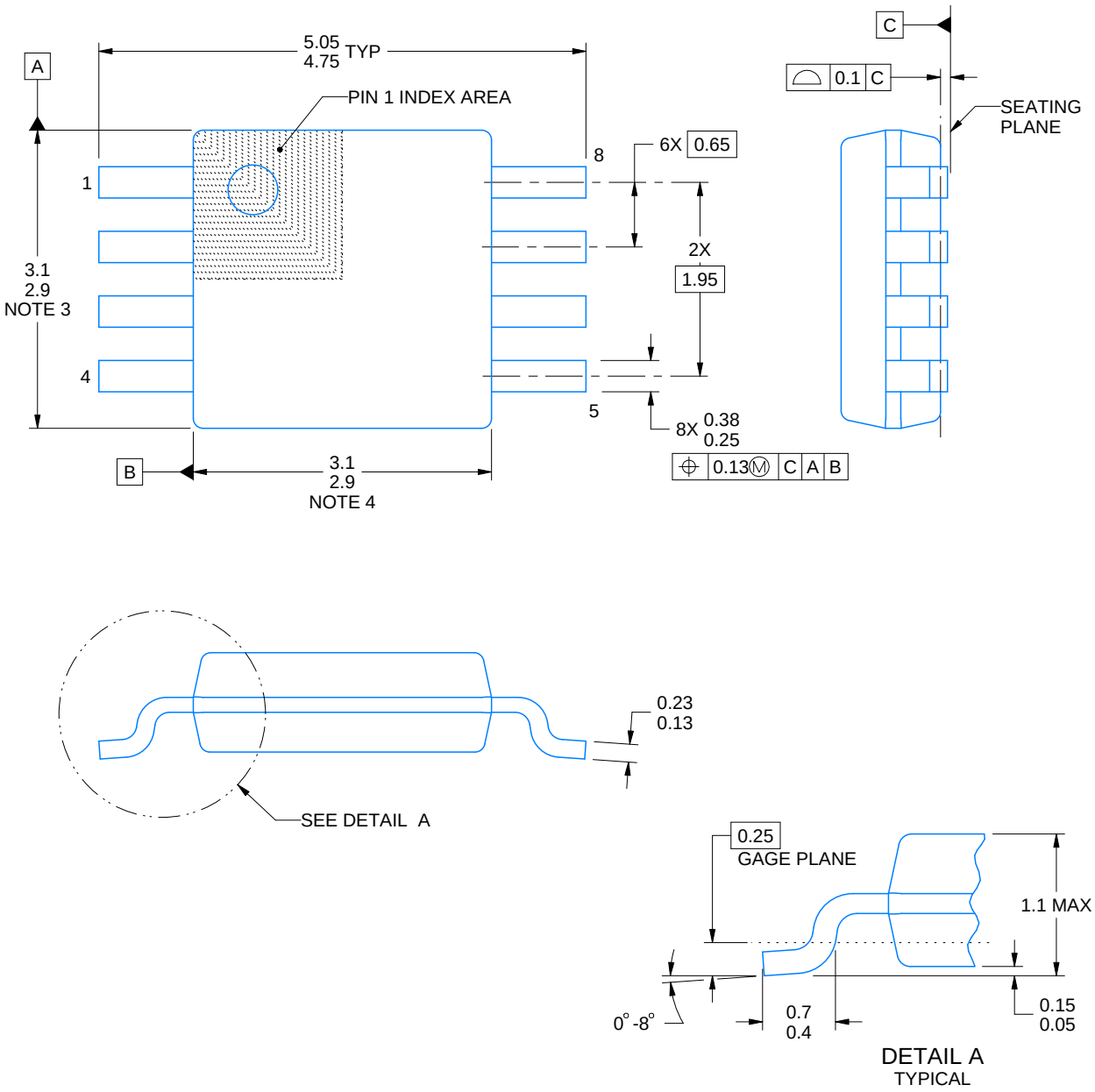
8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DGK0008A

VSSOP - 1.1 mm max height

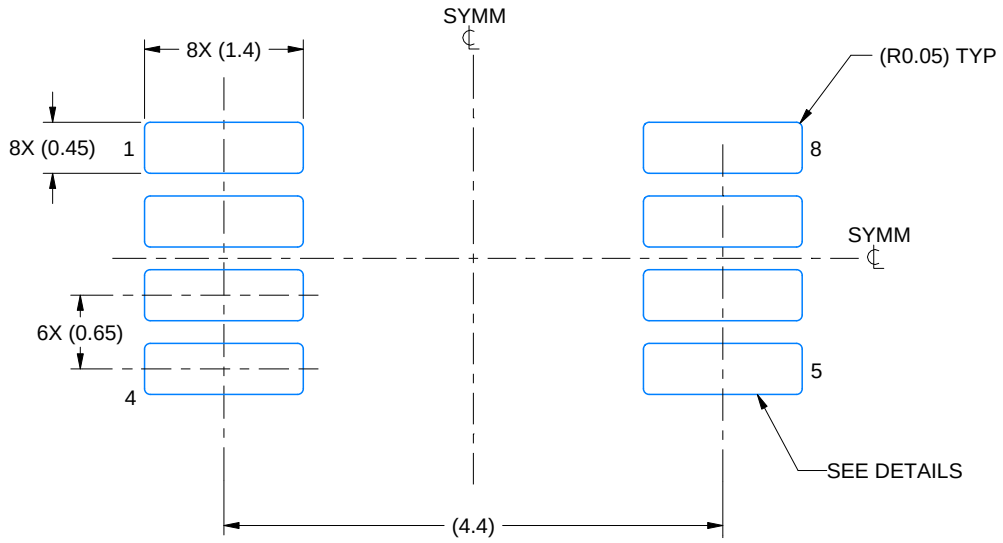
SMALL OUTLINE PACKAGE



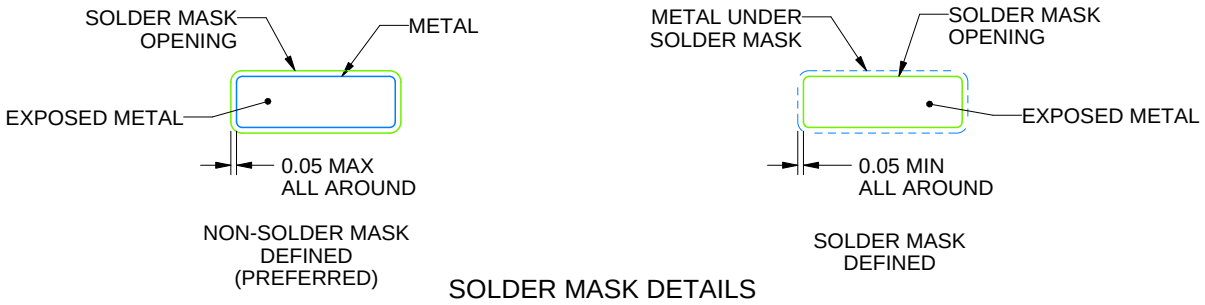
PowerPAD is a trademark of Texas Instruments.

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-187.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 15X

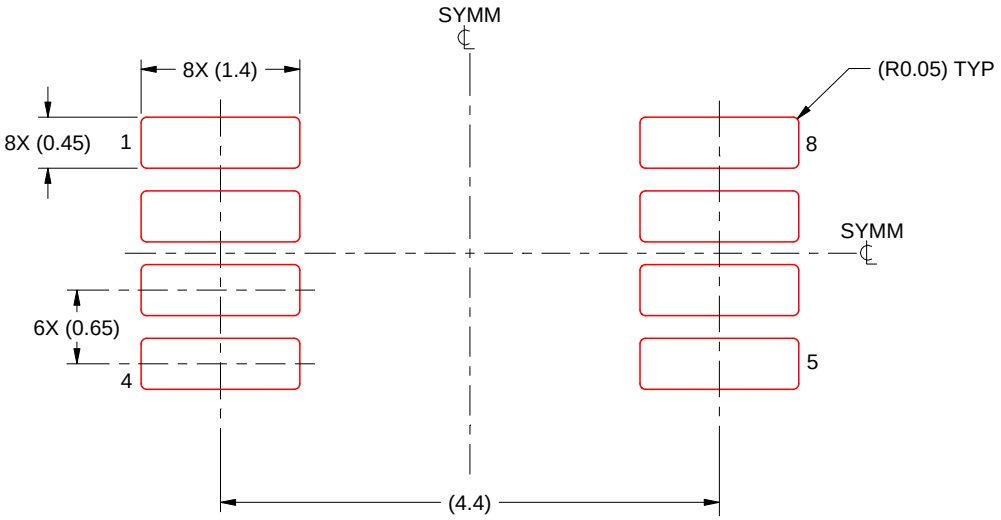


SOLDER MASK DETAILS

4214862/A 04/2023

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.
8. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.
9. Size of metal pad may vary due to creepage requirement.



SOLDER PASTE EXAMPLE
SCALE: 15X

4214862/A 04/2023

NOTES: (continued)

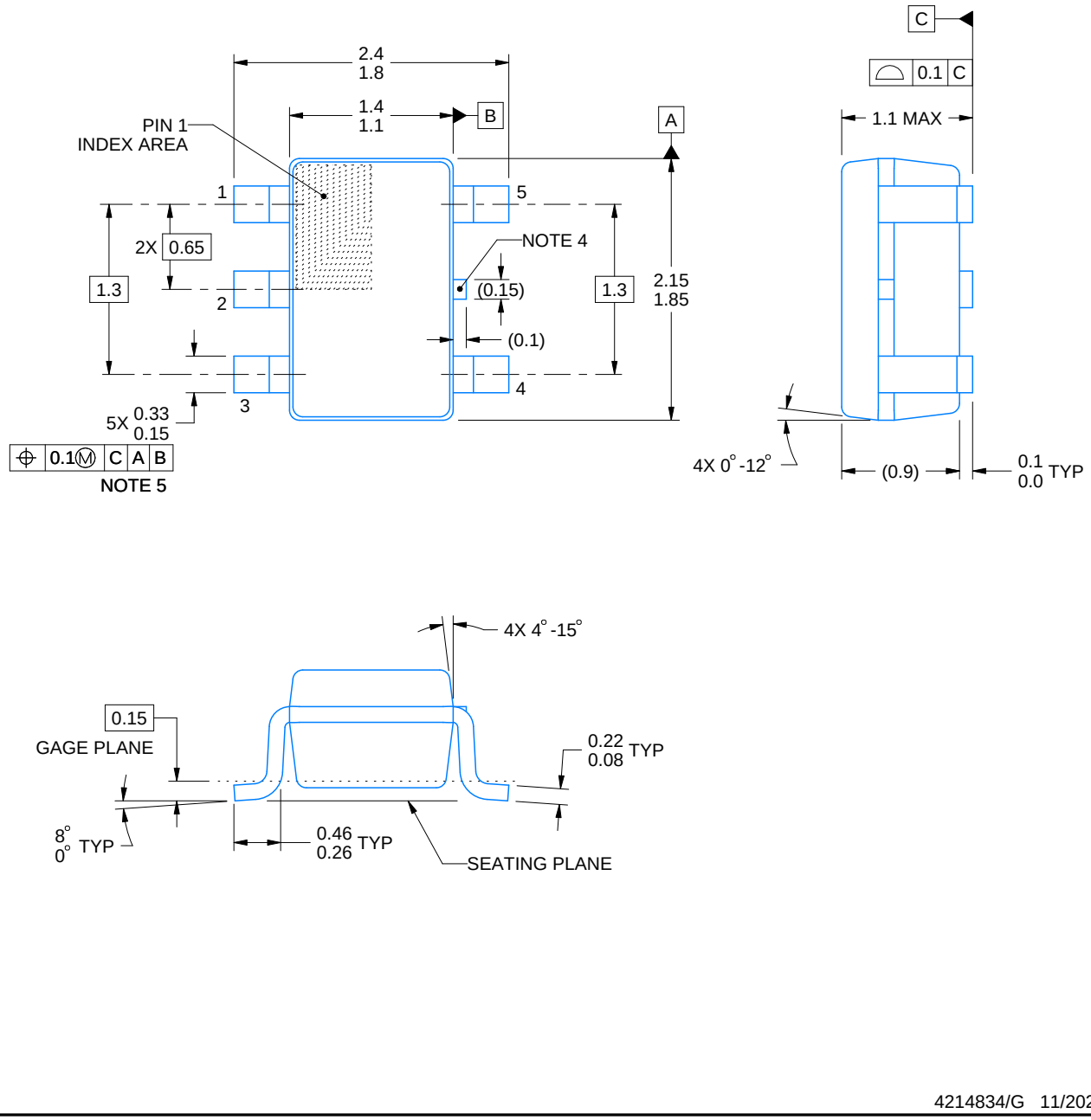
11. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
12. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DCK0005A

SOT - 1.1 max height

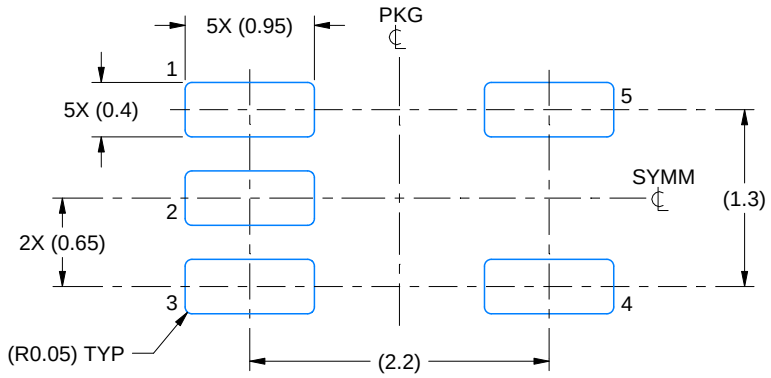
SMALL OUTLINE TRANSISTOR



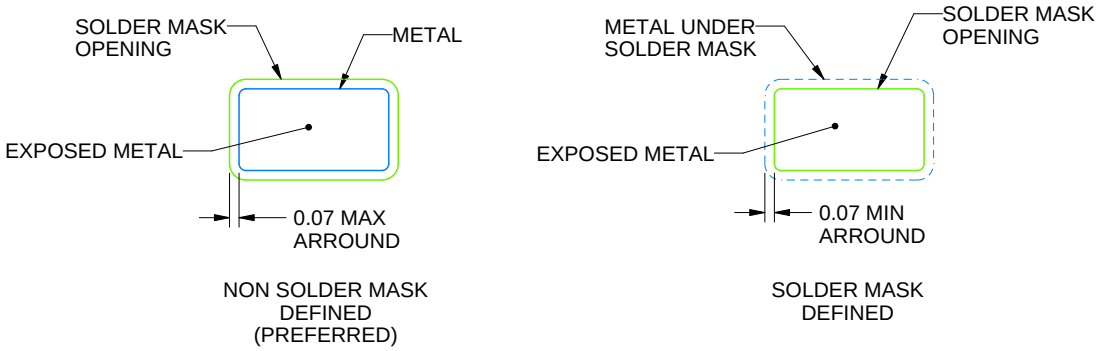
4214834/G 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Refernce JEDEC MO-203.
4. Support pin may differ or may not be present.
5. Lead width does not comply with JEDEC.
6. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25mm per side



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

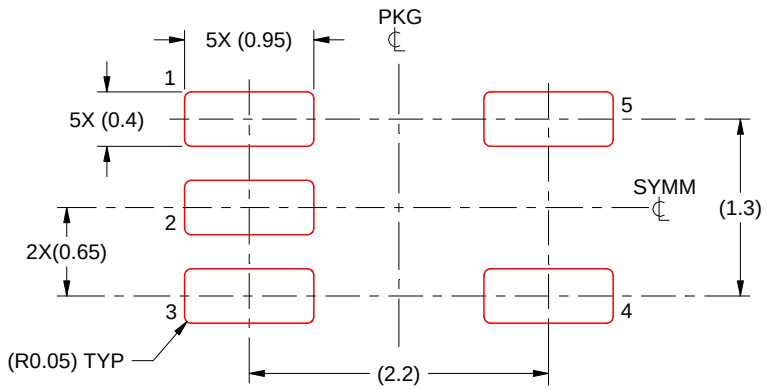


SOLDER MASK DETAILS

4214834/G 11/2024

NOTES: (continued)

7. Publication IPC-7351 may have alternate designs.
8. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 THICK STENCIL
SCALE:18X

4214834/G 11/2024

NOTES: (continued)

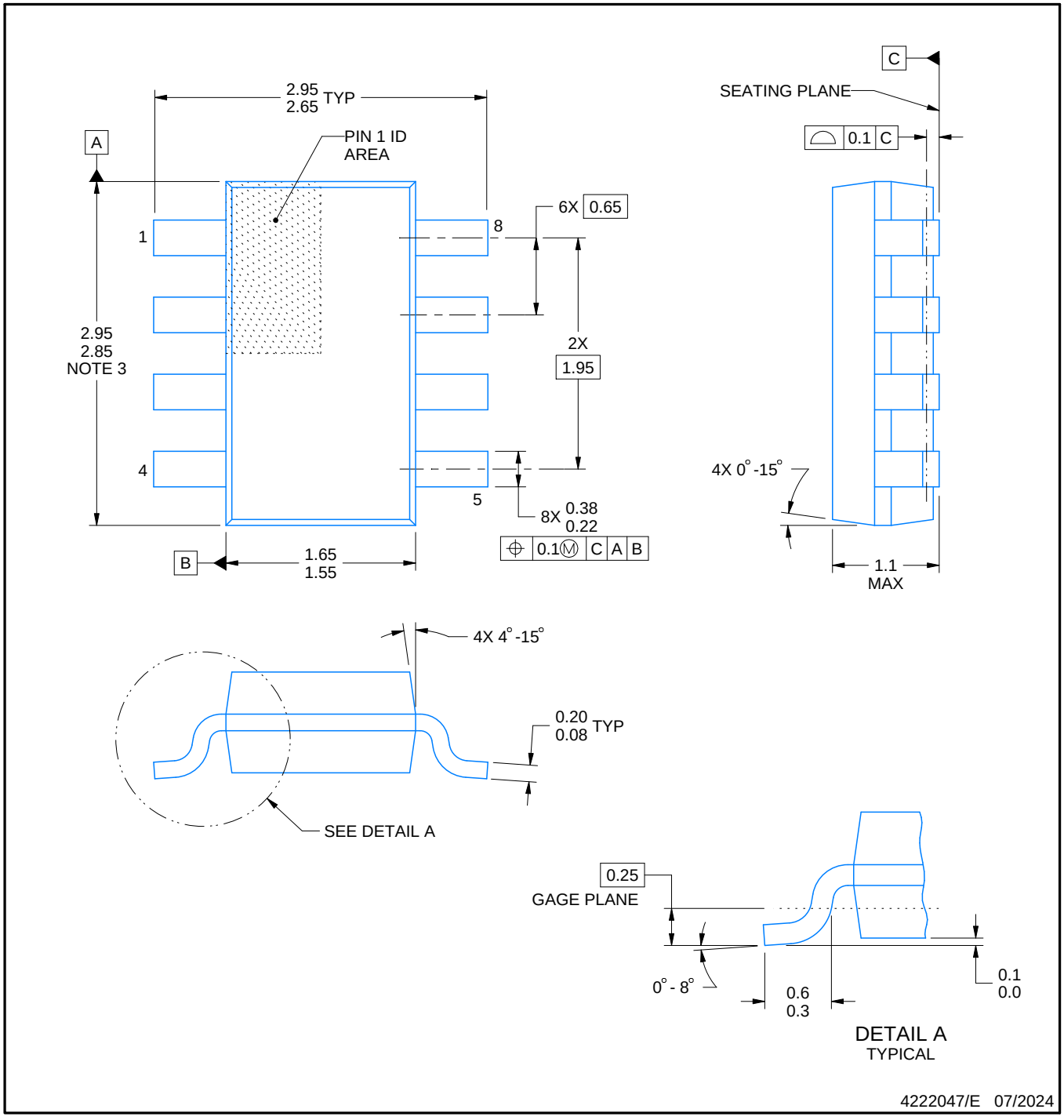
9. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
10. Board assembly site may have different recommendations for stencil design.

PACKAGE OUTLINE

DDF0008A

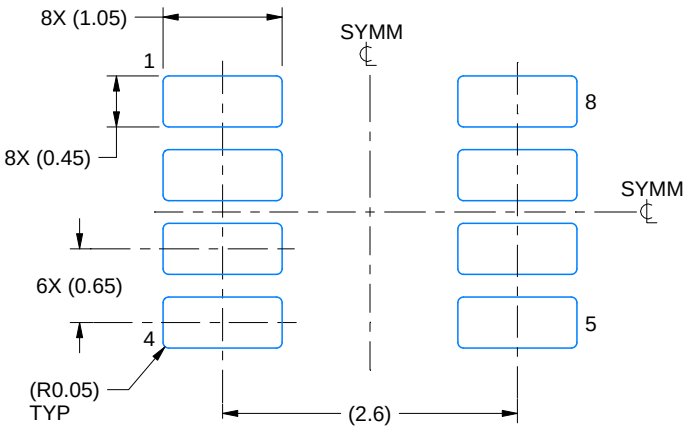
SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE

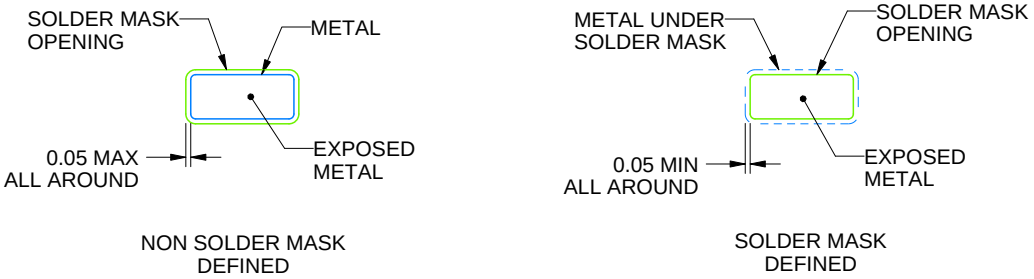


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:15X



SOLDER MASK DETAILS

4222047/E 07/2024

NOTES: (continued)

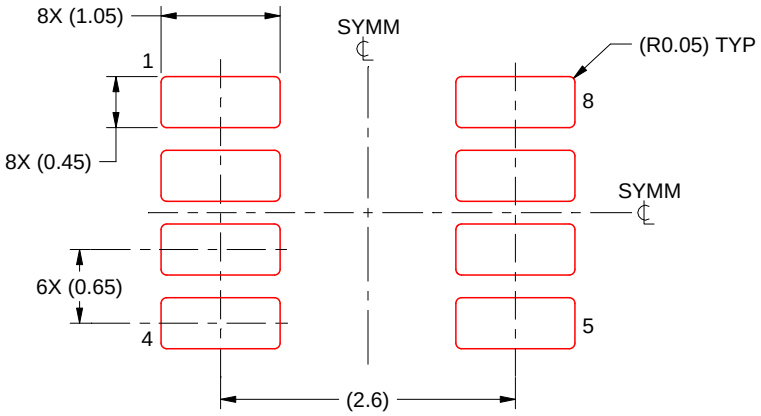
4. Publication IPC-7351 may have alternate designs.
5. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

DDF0008A

SOT-23-THIN - 1.1 mm max height

PLASTIC SMALL OUTLINE

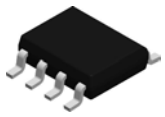


SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE:15X

4222047/E 07/2024

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
7. Board assembly site may have different recommendations for stencil design.

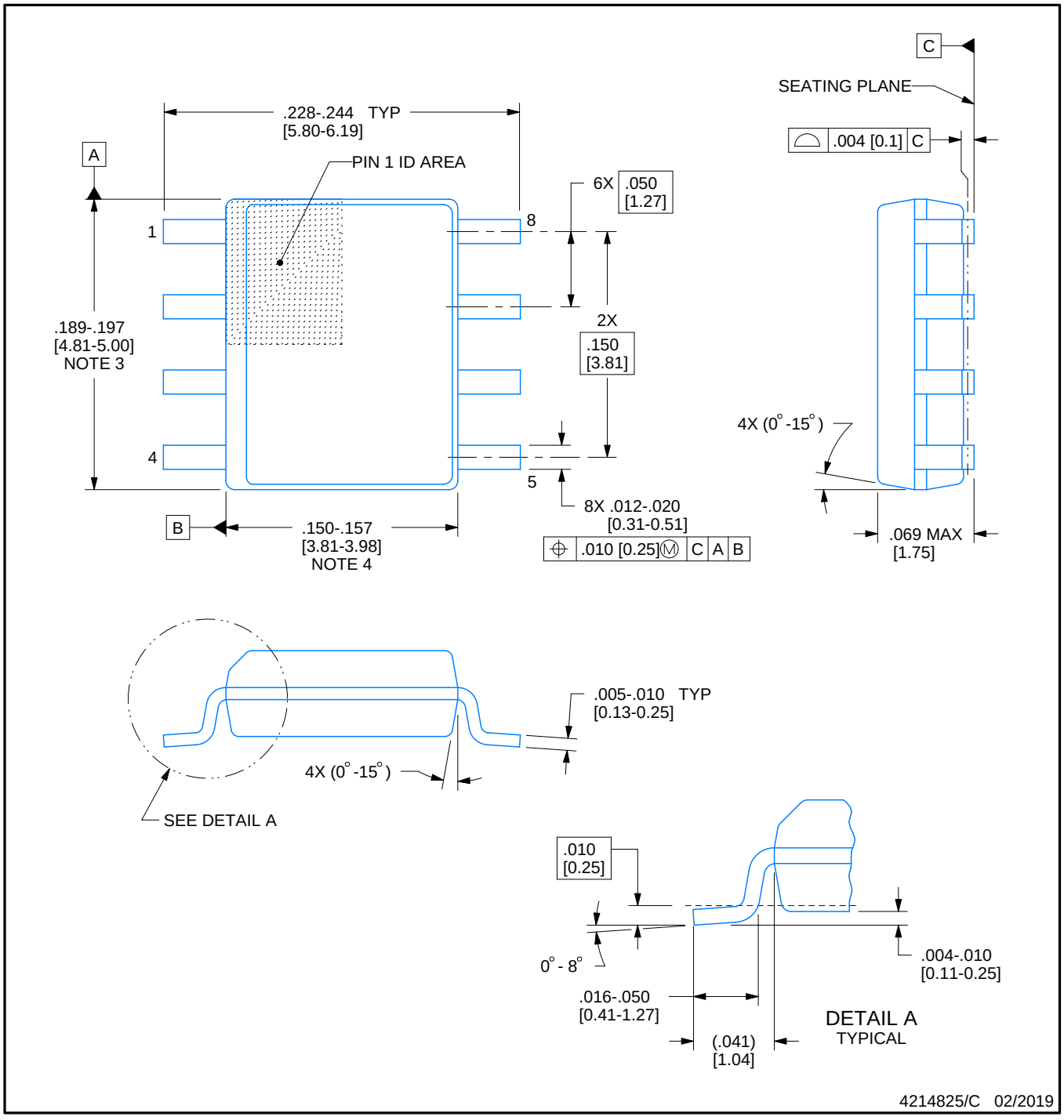


PACKAGE OUTLINE

D0008A

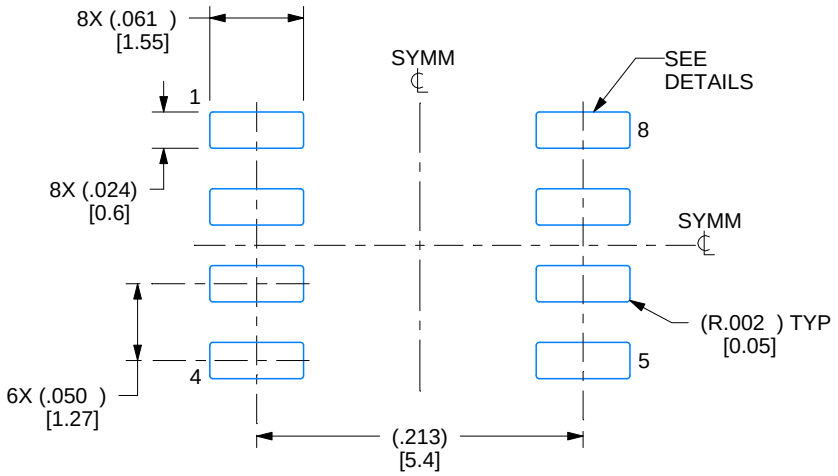
SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT

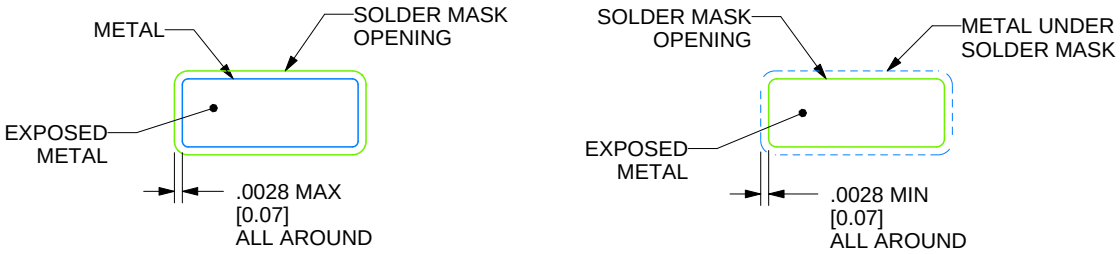


NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
4. This dimension does not include interlead flash.
5. Reference JEDEC registration MS-012, variation AA.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:8X



SOLDER MASK DETAILS

4214825/C 02/2019

NOTES: (continued)

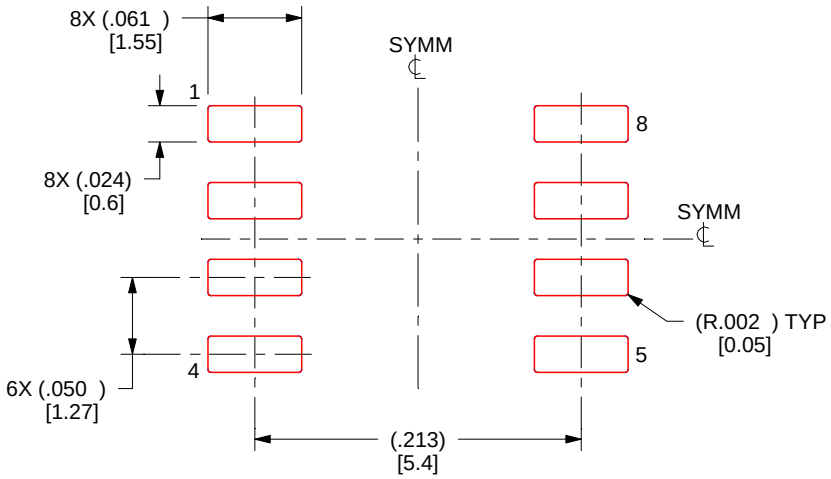
6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

EXAMPLE STENCIL DESIGN

D0008A

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



SOLDER PASTE EXAMPLE
BASED ON .005 INCH [0.125 MM] THICK STENCIL
SCALE:8X

4214825/C 02/2019

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

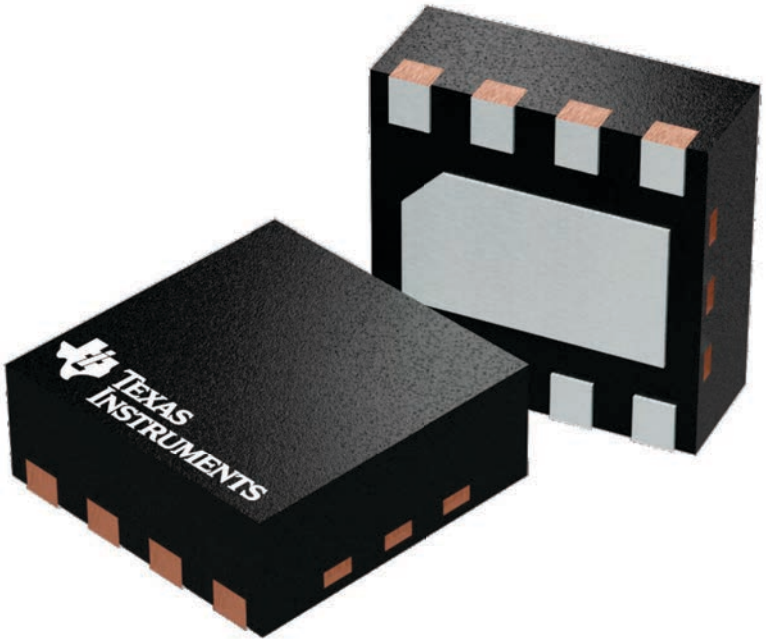
DSG 8

WSON - 0.8 mm max height

2 x 2, 0.5 mm pitch

PLASTIC SMALL OUTLINE - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



4224783/A

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